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Joseph Rozario Michigan Technological University

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THE EFFECT OF ANNEALING ON AMORPHOUS SILICON BASED SOLAR PHOTOVOLTAIC THERMAL SYSTEM (PV/T) AND APPROPRIATE GLOBAL DISPATCH STRATEGIES

By

Joseph Rozario

A thesis submitted in partial fulfillment of the requirements for the degree of

MASTER OF SCIENCE

In Electrical Engineering

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2014

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This thesis has been approved in partial fulfillment for the requirements for the Degree of MASTER OF SCIENCE in Electrical Engineering.

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PREFACE

In the present era of sustainable development, amorphous silicon based solar cells have the potential to contribute to the elevating energy demand and produce clean energy. The economic viability and the dual operation of thermal/ solar power collection makes amorphous silicon based PV/T a good candidate for commercial and household application. Being a recent one, the technology has a wide window open ahead with a lot of development opportunities. This study focuses on one of the most unique features of a-Si:H i.e. degradation and annealing effect and portrays technically sound global dispatch mechanism. The study is conducted under supervision of Dr. Joshua M. Pearce with approval from the Department of Electrical and Computer Engineering, Michigan Technological University. This thesis is composed of two papers, one of which is published and one submitted for publication. The author's contributions are described hereafter.

The methodology of Chapter 2 and the results of Chapter 3 are "The effects of dispatch strategy on electrical performance of amorphous silicon-based solar photovoltaic-thermal systems" published in *Renewable Energy* 68, pp. 459–465 (2014). This article was written by J. Rozario, A.H. Vora, S.K. Debnath, M.J.M. Pathak, and J.M. Pearce. J. Rozario's contribution to this paper was helping with the literature review, revising the simulation code and completing the simulations, remaining analysis, results, figures, writing, and multiple revisions. A.H. Vora and S.K. Debnath's contributions was starting the simulation code and helping with the literature review and the writing. M.J.M. Pathak helped with the literature review and made the experimental measurements. J. M. Pearce's contribution was writing, editing, and consultation.

The results of Chapter 4 are "Optimization of annealing cycles for electric output in outdoor Conditions for amorphous silicon photovoltaic thermal systems" to be published by J. Rozario and J. M. Pearce. J. Rozario's contribution to this paper was the literature review, writing the simulation code and completing the simulations, remaining analysis, results, figures, writing, and multiple revisions. J. M. Pearce's contribution was writing, editing, and consultation.

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LIST OF ABBREVIATIONS

AM1.5	Airmass 1.5
a-Si	Amorphous Silicon
a-Si:H	Hydrogeneted Amorphous Silicon
AZO	Azobenzene Compound
CMOS	Complementary Metal-Oxide-Semiconductor Field Effect Transistor
c-Si	Crystalline Silicon
DSS	Degraded/Degenerated Steady State
ITO	Indium Tin Oxide
PECVD	Plasma Enhanced Chemical Vapor Deposition
p-i-n	p type-intrinsic layer-n type
PV	Photovoltaic
PV/T or PVT	Solar Photovoltaic Thermal System
Si-HJT	Silicon Heterojunction
SnO ₂ :F	Fluorine Doped Tin Dioxide
SWE	Staebler- Wronski Effect
ТСО	Transparent Conducting Oxide

ABSTRACT

Previous work has shown that high-temperature short-term spike thermal annealing of hydrogenated amorphous silicon (a-Si:H) photovoltaic thermal (PVT) systems results in higher electrical energy output. The relationship between temperature and performance of a-Si:H PVT is not simple as high temperatures during thermal annealing improves the immediate electrical performance following an anneal, but during the anneal it creates a marked drop in electrical performance. In addition, the power generation of a-Si:H PVT depends on both the environmental conditions and the Staebler-Wronski Effect kinetics. In order to improve the performance of a-Si:H PVT systems further, this paper reports on the effect of various dispatch strategies on system electrical performance. Utilizing experimental results from thermal annealing, an annealing model simulation for a-Si:Hbased PVT was developed and applied to different cities in the U.S. to investigate potential geographic effects on the dispatch optimization of the overall electrical PVT systems performance and annual electrical yield. The results showed that spike thermal annealing once per day maximized the improved electrical energy generation. In the outdoor operating condition this ideal behavior deteriorates and optimization rules are required to be implemented.

CHAPTER 1

Introduction

For the past few decades the semiconductor industry is mostly dominated by silicon based technologies. Although silicon has an indirect band-gap, no other technology has surpassed the popularity of silicon based technology due to its abundance, state of the art native insulating oxide and nitride with high dielectric constants and good electro-thermal properties. With the development of hetero-structure devices based on II-VI and III-V semiconductors the complementary-metal-oxide-semiconductor (CMOS) technology based on silicon is still the most important device in the industry. Even the photovoltaic industry has adopted silicon based technology commercially. Photovoltaic (PV) is a sustainable and pollution free technology that converts sunlight directly into electricity. In recent years, significant growth has been observed in this green energy sector. The reliability and the environment friendly features of PV have made it unique among the renewable energy and sustainable technology disciplines. In its interaction with the built environment, PV is becoming part of the daily experience of citizens in developed countries as millions of PV modules are installed every year [1]. Alongside the environmental aspects the solar energy harvesting of PV technology has a positive impact on economy as well. As a whole in US, the solar energy industry grew a total of 67% between 2009 and 2010 nationally and is now responsible for over 100,000 jobs, in over 5,000 businesses [2]. In order to manage solar industry to play a more prominent role in economy and to be economically competitive improving the efficiency of the cells and lowering their manufacturing costs is necessary.

1.1 Background

The availability of solar energy far exceeds any conceivable future energy demands. It is environmentally clean, and carbon free technology. Present day's commercial solar cells, most often made from silicon; typically convert sunlight into electricity with an efficiency of only 10 percent to 20 percent [3]. Given their manufacturing costs, these solar modules incorporated in the power grid produce electricity at a cost roughly 3 to 6 times higher than current prices, or 18-30 cents per kilowatt hour [3]. Thus the present day researches mostly focus on improving the cell efficiency and lowering the manufacturing costs. It has been reported that the standard PV cells based on Si has theoretical efficiency of 31% and PV cells based on other novel materials has shown a maximum of 40% experimental efficiency [3]. According to the latest NPD Solarbuzz_PV Equipment Quarterly report, the polycrystalline Si solar modules are expected to dominate the industry in 2014 with p-type poly c-Si technology accounting for 62% of all modules produced [4].

Mono and poly crystalline silicon (c-Si) solar photovoltaic (PV) cells are used in the largest quantity on the market, representing about 80-90% of the world total PV cell production according to data obtained in 2012 [5]. The highest energy conversion efficiency reported so far for experimental crystalline silicon PV cells is 25% [6]. High-efficiency research PV cells have advantages in performance but are often unsuitable for low-cost production due to their complex structures, high temperature procedures and the prolonged manufacturing processes required for fabrication [6]. High energy conversion efficiency and low processing cost can only be achieved simultaneously through the development of advanced production technologies and equipment. One good alternative with minimized costs can be silicon heterojunction technology (Si-HJT) which allows solar cells with energy conversion efficiencies above 20 % at industrial-production level [7]. Thin film Si solar cells consist of thin amorphous silicon (a-Si) layers on monocrystalline silicon wafers. The key feature of these structures is the displacement of highly recombination-active (ohmic) contacts from the crystalline surface by insertion of a wide bandgap intrinsic film [7]. Also to obtain full device potential, the hetero-interface state density is required to be at its minimum [7]. In reality, hydrogenated amorphous silicon (a-Si:H) films of only a few nanometer thickness are suitable selection for this. Their bandgap is wider than that of crystalline silicon (c-Si) and intrinsic films of hydrogenated a-Si can reduce the c-Si surface state density [7]. Additionally, doping of these films is easier (either n- or p-type) and allows lithography-free fabrication of contacts with low saturation-current density [7]. The technology involved in growing amorphous silicon is relatively easier and simple compared to growing crystals. The optical property of a-Si:H is also superior to c-Si and that makes them promising for collecting solar energy as the active layer. The absorption coefficient of a-Si:H is high with minimized reflection compared to c-Si [8]. That point out the fact that for the same light energy absorption a-Si:H requires thinner layers compared to c-Si. That implies that comparatively less materials are required for making PV cells out of a-Si:H than from c-Si [9]. Therefore besides the a-Si:H/c-Si heterojunction technology other photovoltaic cells based on p-i-n a-Si:H device structures has promising future in PV market.

One unique application of hydrogenated amorphous silicon (a-Si:H) can be photovoltaic thermal hybrid solar collectors, also known as hybrid PV/T systems or PVT, are systems that convert solar radiation into thermal and electrical energy. These systems combine a photovoltaic cell with a solar thermal collector and perform dual operation- 1) converts light energy i.e. photons into electricity and 2) captures the remaining energy and collects waste heat from the PV module. The capture of both heat and electricity allow these devices to have higher exergy [10] and thus be more overall energy efficient than stand-alone solar photovoltaic (PV) or solar thermal [11].

Photovoltaic cell efficiency falls with the rise in temperature due to increased resistance. Employing PV/T's can be advantageous in the way that it carries heat away from the modules thereby cooling the cells and thus improving their efficiency by lowering resistance [12]. Although this is a more successful method, it causes the thermal component to under-perform compared to a stand-alone solar thermal collector. Photovoltaic materials with low temperature coefficients such as amorphous silicon PV allow the PV/T to be operated at high temperatures, promoting a more unified PVT system.

1.2 Hydrogenated Amorphous Silicon in Photovoltaic Thermal System

Despite improvements in solar photovoltaic (PV) efficiency, which reduces the cost of PV generated electricity to competitive levels in some markets [13], in conventional cells much of the radiation above the bandgap does not contribute to electrical energy generation and instead is wasted as heat. On the other hand, solar thermal systems, which have the potential for high efficiencies, have low exergy values [14]. Thus, developing photovoltaic solar thermal (PVT) systems offer a distinct advantage over simple PV or low exergy solar thermal systems by utilizing this waste thermal energy from the PV absorber for heating applications [15]. PVT offers advantages in overall exergy, energy and cost [14-21]. Historically, most of the PVT systems were developed using crystalline silicon (c-Si) PV, which have a thermal coefficient of -0.45%/K [22]. Because of this relatively large thermal coefficient c-Si-based PVT systems are designed to cool the c-Si PV modules in order to maximize the electrical output and extracted thermal energy is considered as secondary benefit. This results in non-optimization of c-Si-based PVT systems because the thermal component under-performs when compared to standard solar thermal collectors [23-27].



Fig. 1.1 Temperature Vs efficiency plot for crystalline and amorphous silicon PV cells

Thin-film hydrogenated amorphous silicon (a-Si:H) solar cells, however, have a thermal coefficient of only 0.13%/K [22], which makes it suitable for high temperature applications that are not possible with c-Si PV due to what would be significant electrical output losses at high operating temperatures. Unlike c-Si the efficiency drop with temperature is negligible in amorphous silicon cells. Figure 1.1 shows the temperature versus efficiency plot for commercially manufactured c-Si and a-Si PV cells. The biggest technical challenge confronting a-Si:H PV is a light-induced degradation of performance known as the Staebler-Wronski effect (SWE) [28-32]. This effect is associated with the creation of defect states in the a-Si:H material when exposed to sunlight, which causes a reduction in efficiency of the solar cells with exposure time [29]. These defects states tend to saturate after an extended exposure to sunlight (approximately 100 h under continuous 1 sun illumination) and this stabilized state is referred as degraded steady-state (DSS) [33,34]. However, it has been found that SWE is reversible in nature and the performance (efficiency) of a-Si:H solar cell can be returned to its initial state if the cell is heated to 150 °C for 4 h as the defect states are annealed [29,33,35,36] although the defect states can anneal at lower temperatures over more extended time periods [33]. Reducing SWE is viewed as so important, that Pola et al. have even suggested removing entire PV arrays and annealing the modules in a hot air oven at lower temperatures (e.g. at 80 °C) over extended times [37]. Additionally, because of this effect it has been reported that a-Si:H PV performs better at high temperatures in view of the fact that optoelectronic properties of a-Si:H materials [28,38,39] stabilize at a higher efficiency at higher temperatures [34,40]. Operating at elevated temperatures is highly desirable for PVT hybrid systems as the solar thermal efficiency increases with temperature. For a solar thermal flat plate collector a temperature of 100 °C can be easily achieved and if the system is stagnated it can even climb higher than 200 °C [41]. Therefore, direct deposition of a-Si:H PV over flat plate solar collectors can facilitate high-temperature operation where the PV panel could be in-situ annealed and simultaneously increasing overall system exergy [42-44]. It has also been experimentally demonstrated that high temperature operation and regular high temperature spike thermal annealing for 1 h at 100 °C on a 12 h cycle can result in higher energy and exergy output [45]. However, a dispatch strategy

is required to optimize the usage of available resources to meet the electrical and thermal demand and to maximize the overall system efficiency. Although spike thermal annealing of a-Si:H PV panels with short thermal spikes can improve the immediate electrical performance following an anneal, the annealing process at high temperatures creates a marked drop in electrical performance over the annealing period (it can also deteriorate the overall thermal performance of the system as the thermal energy required for spike annealing is not being extracted). It has also been observed that, the degraded steady state is obtained more rapidly at higher temperature at a higher power [45]. Therefore a dispatch strategy is required to optimize the number of required spike thermal annealing cycles in order to maximize the overall system performance including the thermal and electrical output.

1.3 Objective

The present work reports on the effects of various dispatch strategies on the first of these outputs- the electrical system performance. Utilizing experimental results from thermal annealing, an annealing model simulation for a-Si:H-based PVT was developed and applied to different cities (Goldendale, San Antonio, Reno and Las Vegas) in U.S. to investigate the effects of geographic optimization on the overall electrical PVT systems performance. The aim and objective are following:

- I. Analyze the degradation data set for different operating temperature.
- II. Derive suitable equations that take into account the light-induced degradation effect of a-Si:H PV cell at different operating temperatures. Required for identifying the fitting curve for the reference data.
- III. Develop a simulation model that combines the degradation and spike annealing effects and calculate additional energy generation. This explains the annealing effect under 1 sun (1000 W/m² solar irradiation) illumination.
- IV. Input real time solar irradiation data collected for different cities in the simulation model in order to observe the real world scenario.

- V. Observe the real time simulation results while employed in specific cases of dispatch strategies. Evaluate the outcome from different dispatch strategies. Required for determining the ideal dispatch strategy.
- VI. Observe non-ideal cases. Determine factors playing major roles over dispatch strategies.

1.4 Device Structure and Degradation Characteristics

The contemporary work utilizes Pathak et al.'s device structure and experimental data as the reference model for device layout and light-induced degradation spike annealing characteristics of thin film a-Si:H PV cells [45]. The cell being considered in the simulation model has an i-layer thicknesses of 630 nm- deposited on transparent conducting oxide (TCO) glass substrate, prepared in plasma enhanced chemical vapor deposition (PECVD) system. Fig. 1.2 shows the device configuration used in this investigation include following layers from bottom to cell up: AGC float glass (3 mm)/SnO₂:F (700 nm)/Ag (200 nm)/AZO (100 nm)/n-a-Si:H 25 nm/i-a-Si:H 630 nm/p-a-Si:H 15 nm/ITO 70 nm. Fig. 1.3 shows the light induced degradation characteristics for the reference cell at operating temperatures 25 °C, 50 °C and 90 °C respectively.



Fig. 1.2: Composition and structure of the a-Si:H solar photovoltaic cell (device with 630 nm i-layer thickness considered as reference model) [45]



Fig. 1.3: A normalized temperature series of 25, 50 and 90 °C degradation under 1 sun for a PV cell with an i-layer thickness of 630 nm [45]



Fig. 1.4 Comparison of the same 630 nm i-layer thick a-Si:H PV cell degraded at 50 °C under 1 sun (Normal Degradation) to results obtained for degradation at 50 °C under 1 sun coupled with spike annealing at 100 °C on a 12 h cycle for 192 h (Spike Annealing) [45]

Fig. 1.4 shows the spike-annealing effect at operating temperature 50 $^{\circ}$ C. The reference data clearly shows additional energy generation as a consequence of spike annealing. It should be noted that all of these data were recorded while the device is illuminated at 1 sun (1000 W/m²) solar irradiation.

1.5 Outline

The Chapters are organized in following order:

Chapter 2 '*Methodology*' introduces the simulation and modeling steps, procedures in detail. That includes the modification of equations, curve fitting technique of the reference data, acquisition of real-time data and different cases of dispatch strategies that will be studied.

Chapter 3 '*Results: Ideal Cases*' concentrates on the obtained simulation results at sustained operating temperature conditions. The results obtained for 1 sun illumination are discussed in thorough. Real-data simulation results for different dispatch strategies are also presented in this section.

Chapter 4 '*Results: Outdoor Temperature Simulation*' focus mostly on the effects of temperature and geographic position on degradation associated parameters and how annealing influence device outcome at outdoors. This chapter also discusses about the appropriate dispatch strategies.

Chapter 5 *Discussion, Future Work and Conclusions* summarizes the notations made from earlier discussion and directs toward a suitable conclusion. It also discuss about the future scope of this fascinating technology.

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CHAPTER 2

Methodology

2.1 PV/T System^{*}

The PVT system shown schematically in Fig. 2.1 was used for modeling and simulation in the present work. The a-Si:H PV is connected to an inverter that powers the AC load and the heat generated by the PVT is transferred to thermal load by a heat exchanger. A temperature controller is used to control both this heat flow and the regular thermal annealing, which is provided by the heat generated from the PVT itself. High temperature spike thermal annealing for 1 h at 100 °C at regular cycles is carried in order to reverse Staebler-Wronski effect (SWE).



Fig. 2.1: Schematic of a-Si:H-based PVT system

^{*} The material contained in this chapter was previously published in the journal, *Renewable Energy*, volume 68, pp. 459-465, August 2014.

2.2 Calculation Method

Usually a-Si:H-based PV exhibit power degradation due to 1) the temperature effect, exhibited by all solar cells and 2) SWE, which is a long-term light exposure effect, which is a unique characteristic of a-Si:H-based solar cells. The total energy generated by the PV of power, *P*, for a year is given by:

$$E = \sum_{n=1}^{365 \times 24} P_n t \tag{2.1}$$

where P_n is the power produced in the *n* th hour and *t* is time, which is 1 h in this case. The maximum power, $P_{max}(T)$, at a temperature *T* from reference temperature (T_{ref}) having a temperature coefficient of γ is given by [1]:

$$P_{max}(T) = \frac{P_{max(ref)}}{\left(1 + \gamma(T_{ref} - T)\right)} \cdot \frac{S}{S_{ref}} \cdot \frac{1}{\left(1 + \delta \ln\left(\frac{S}{S_{ref}}\right)\right)}$$
(2.2)

where *S* and *S_{ref}* are the irradiance and reference irradiance level respectively, *P_{max(ref)}* is the maximum power at a reference temperature *T_{ref}*, which is 25 °C, *S_{ref}* is equal to 1000 W/m², γ is -0.0020/°C, δ is +0.063 [1]. Eq. (2.2) is used to calculate the power with no thermal annealing and universally applicable to any solar cells.

Eq. (2.2) does not take SWE into account and must therefore be modified with an exponential term that is governed by the aggregate exposure to solar flux from the annealed state and the operating temperature. The exponential terms were determined by curve fitting the experimental results of Pathak et al. [2] as shown in Fig. 2.2.



Fig. 2.2 Experimental data showing degenerated steady state obtained at temperatures 25 °C, 50 °C, and 90 °C respectively for a-Si:H PV cell active layer thickness of 630 nm under 1 sun (source: Pathak et. al.) [2] and exponential fits using equation (2.3)

Fig. 2.2 shows the experimentally obtained data for degenerated steady states at different temperatures for a-Si:H based PV/T with i-layer thickness of 630 nm under 1 sun (1000 W/m² irradiance) for 600 h. For a-Si:H PVT the modified form of Eq. (2.2) is altered to be:

$$P_{max}(T) = \left(\frac{P_{\max(ref)}}{\left(1 + \gamma(T_{ref} - T)\right)} - k_{dss} \cdot P_{\max(ref)} \cdot \left(1 - e^{-u_{dss} \cdot t}\right)\right) \cdot \frac{s}{s_{ref}} \cdot \frac{1}{\left(1 + \delta \ln\left(\frac{s}{s_{ref}}\right)\right)}$$
(2.3)

The values of the parameters k_{dss} and u_{dss} were obtained by analyzing the experimental data and their values vary with temperature. For the temperatures 25 °C, 50 °C, and 90 °C, k_{dss} has the values 0.3450, 0.2154, and 0.07917 respectively; and u_{dss} has the values 0.03601, 0.07552 and 0.2097 respectively as determined from Fig. 2.2. It should be noted that as the temperature rises k_{dss} decreases and u_{dss} increases, as is consistent with prior SWE studies of a-Si:H PV [3-5].

2.3 Dispatch Strategy

During annealing the temperature rises rapidly from normal operating temperature to high temperature (~ 100 °C) for a short duration (1 h) and this reduces electrical performance. The power drops rapidly as the temperature is increased for the anneal and then starts to rise slowly as the annealing continues. For simplification of the model the annealing period is considered constant at the reduced power.

Case	Dispatch Strategy	Note
Case I	Without annealing under 1 sun	PVT operating temperature of 25 °C,
		50 °C, and 90 °C respectively without
		spike annealing
Case II	Without annealing under normal	PVT operating temperature of 25 °C,
	sun	50 °C, and 90 °C respectively without
		spike annealing
Case III	With 48 hr annealing cycle (under 1	Spike annealing performed once
	sun and normal sun)	every other day between hours 8 and
		9
Case IV	With 24 hr annealing cycle (under 1	Spike annealing performed once per
	sun and normal sun)	day between hours 8 and 9
Case V	Annealed twice per day (under 1	Spike annealing performed twice per
	sun and normal sun)	day during the peak sun hour time
		period (hour 8-15) with 4 hours
		interval
Case VI	Annealed three times per day	Spike annealing performed thrice per
	(under 1 sun and normal sun)	day during the peak sun hour time
		period (hour 8-15) with 2 hours
		interval

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Table 2.1 Cases for	the dispatch strategy of	spike annealing of	$a-S_1$: H type PV/T

Case VII	Annealed four times per day (under	Spike annealing performed 4 times
	1 sun and normal sun)	per day during the peak sun hour time
		period (hour 8-15) with 1 hour
		interval
Case VIII	Annealed five times per day (under	Spike annealing performed 5 times
	1 sun and normal sun)	per day during the time period (hour
		7-16) with 1 hour interval
Case IX	Annealed six times per day (under 1	Spike annealing performed 6 times
	sun and normal sun)	per day during the time period (hour
		7-17) with 1 hour interval

Table 2.1 shows a list of different case studies (depicting different dispatch strategies) for which the simulation was performed. 1 sun solar irradiance has a constant value of 1000 W/m² and has a AM1.5 spectrum. Here 'normal sun' solar irradiance is defined as the standard hourly solar irradiance from the sun for a given location. Normal sun conditions vary over the day with real outdoor conditions. For all the above cases, the model was simulated at outdoor conditions and for various geographic locations for a year (February 1st, 2012 - January 31st, 2013) in the U.S. to better understand real-world significance of this type of PVT system under different dispatch strategy. Four different cities, namely Goldendale (Klickitat county, Washington), San Antonio (Valles Caldera, New Mexico), Reno (UNR campus, Nevada) and Las Vegas (Southern Nevada) were chosen on the basis of different dispatch strategies. The details for the locations are shown in Table 2.2 [6, 7].

City	Location	Average Air and	Altitude	Average
		Soil Temperature		hourly solar
				irradiance
Goldendale (Klickitat	45°49'16" N	9.4 °C, 11.5 °C	1636 ft.	179.09 W/m^2
county, Washington)	120°49'17" W			
San Antonio (Valles	35°58'50" N	5.3 °C, 7 °C	8523 ft.	206.7 W/m^2
Caldera, New	106°34'15" W			
Mexico)				
Reno (Nevada)	39°32'21" N	12.5 °C, 15.1 °C	4480 ft.	224.6 W/m^2
	119°48'21" W			
Las Vegas (Southern	36°06'51" N	22.3 °C, 24.9 °C	2025 ft	231.0 W/m^2
Nevada)	115°08'57" W			

 Table 2.2 Summary of climate for cities chosen for simulation [6,7]

The solar irradiance, air temperature and soil temperature data was obtained on hourly basis for the four cities (Goldendale, San Antonio, Reno and Las Vegas) [6,7]. The average hourly solar irradiation data for the above mentioned cities were obtained using Eq. (2.4).

$$S_{i=1 \ to \ 24} = \frac{1}{366} \sum_{n=1}^{366} S_{i,n,city}$$
(2.4)

where S_i is the average solar irradiance for *i* th hour of four cities (averaged yearly), and $S_{i,n,city}$ is the solar irradiance for *i* th hour and *n* th day for a year for a given location. Fig. 2.3 shows the average hourly solar irradiance for the four cities obtained using Eq. (2.4). Average solar irradiance per day for Goldendale, San Antonio, Reno, and Las Vegas are 4.30, 4.96, 5.39, and 5.54 sun hours respectively. With hour 12 being the peak sun of the day the highest sun hour period is between hours 9 and 16 in the day when the solar irradiance is higher than 250 W/m². Therefore spike annealing is used between hours 8 and 15 as seen in Fig. 2.3.



Fig. 2.3: Average hourly solar irradiance for the four cities for whole year (February 1st, 2012 - January 31st, 2013)

From Eq. (2.2) it can be seen that for c-Si-based PV cells more power is obtained at lower temperature with higher irradiance. In case of a-Si:H PV/T the effect of temperature and light intensity is more complicated as long time light exposure causes degradation and thermal annealing improves device performance by reducing defect states. As the exponential component of Eq. (2.3) represents the light induced degraded power therefore deriving a suitable dispatch strategy for a-Si:H PV/T will depend on the PV/T panel temperature, solar irradiance and peak sun hour period of a day. While taking into account the effects of SWE and annealing altogether the exponential component is required to be modified as a function of these parameters which requires further study. In order to determine the annealing effect a set of binary arrays were generated, which take into account the effects of dispatch strategies on hourly power generation. The binary values of these arrays were set based on specific dispatch strategies. The total energy generation over a year for the chosen cities for different operating temperature (i.e. 25 °C, 50 °C and 90 °C) which were obtained by using the hourly recorded standard solar irradiation data. A time period of 8784 hours (i.e. one year) with both 1 sun and normal sun solar irradiation was considered during the execution of the dispatch strategies. The total energy generated for each case over a year was determined to identify the most effective dispatch strategy for chosen geographical locations.

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CHAPTER 3

Results: Ideal Cases

3.1 1-Sun Simulation[†]

At higher temperatures a-Si:H-based solar cells degrade more rapidly initially, but stabilize at a higher power than when operated at lower temperatures [1]. Based on this knowledge, the available data, and temperature guided solar cell degradation principles a suitable equation is proposed which can approximately represent the experimental data. The curve fits for this approximation are shown in Fig. 2.2, which represents the simulation output of dispatch strategy Case I (the control case). The study of Case II calculates the total energy generation over a year for the chosen cities for different operating temperature (i.e. 25 °C, 50 °C and 90 °C) which were obtained by using the hourly recorded standard solar irradiation data. A time period of 8784 h (i.e. one year) with both 1 sun and normal sun solar irradiation was considered during the execution of the dispatch strategies explained in Case III to Case IX. The maximum power (at t = 0) at reference temperature 25 °C which has a value of approximately 5.3 mW for the small test cells. Case-III to Case-IX utilized an annealing operation. Both the values of 1 sun and normal sun energy generation were calculated for each case study.

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Fig. 3.1: Dispatch strategy Case-III: annealing once every other day, for the operating temperatures. a) 25 °C, b) 50 °C, and c) 90 °C at 1 sun.

Fig. 3.1 shows the effect of annealing explained in Case III and degradation for the operating temperatures a) 25 °C, b) 50 °C, and c) 90 °C respectively at 1 sun. In this case annealing is performed (from hour 8 to hour 9) once every two days (after the first day) followed by degradation at a definite operating temperature. Fig. 3.1 shows that the cells generate more power with annealing. As can be seen from Fig. 3.1 at lower temperatures (a and b) of operation SWE dominates and reduces electrical output as expected. In Fig. 3.1c, operating at 90 °C there is very little observable SWE as compared to the lower temperature cases.



Fig. 3.2: Dispatch strategies consisting of Case-IV: annealing once every day, under 1 sun, a) 50 °C degradation and b) 90 °C degradation. Dispatch Strategy Case-IV: annealing twice every day, under 1 sun, c) 50 °C and d) 90 °C degradation. Dispatch Strategy Case-VI: annealing three times every day, under 1 sun, e) 50 °C and f) 90 °C degradation.

Fig. 3.2 shows the dispatch strategies individually for clarity. Fig. 3.2 shows the 1 sun simulation results obtained for Case IV at operating temperatures a) 50 °C and b) 90 °C. The annealing is performed once every day (from 800 to 900 h) followed by a 50 °C, and 90 °C degradation, resulted in greater output than the previous case.

The 1 sun simulation results for Case V at operating temperature 50 °C and 90 °C are shown in Fig. 3.2c and d, respectfully. Annealing is performed twice every day. The interval between two consecutive annealing periods is four hours. Between the annealing cycles a degradation temperature of 50 °C and 90 °C is maintained respectively.

Fig. 3.2e and f shows simulation results for Case VI. Annealing is performed three times a day with an interval of two hours. During the intervals a degradation temperature of 50 $^{\circ}$ C (e) and 90 $^{\circ}$ C (f) is maintained respectively.



Fig. 3.3: Hourly maximum output power for different dispatch strategies under 1 sun (operating temperature 90 °C).

Similar plots were obtained for case studies VII, VIII, and IX. In all these cases simulations were performed for operating temperatures 25 $^{\circ}$ C, 50 $^{\circ}$ C, and 90 $^{\circ}$ C. Finally, area analysis was performed to determine the total energy generated in each cases. Fig. 3.3 shows the hourly maximum output power for different case studies at 1 sun and operating temperature 90 $^{\circ}$ C.

3.2 Simulation Based on Real Time Hourly Solar Irradiance Data

Unlike the 1-sun irradiation, in the outdoor environment the solar irradiance varies frequently. This affects the performance of any solar cell tremendously and when annealing is associated the power generation over a day also fluctuates depending on the applied dispatch strategy. To see how the dispatch strategies influence power throughout the day Fig. 3.4 is used as an example and shows the average hourly power generation in San Antonio for different dispatch strategies. As can be seen in Fig. 3.4, the power curves closely follow the solar irradiance curve shown on the right y-axis.



Fig. 3.4 Average hourly power generation in San Antonio for different case studies. Right Y-axis shows average hourly solar irradiance.



Fig. 3.5 Total energy generation (at operating temperature 25 °C, 50 °C, and 90 °C under 1 sun) over a time period of 8784 hours as a function of the number of anneals per day.

Fig. 3.5 shows the total energy generation over a period of 8784 hours (under 1 sun and at different operating temperatures) with respect to the number of anneals per day. It

is notable that at operating temperature 90 °C and 1 sun irradiance, the energy is maximized for the dispatch strategy of Case IV (annealing once per day). Beyond that at 1 sun irradiance, with increasing the number of anneals per day total energy generation decreases and even drops to lower values than the DSS energy. This can be attributed to the power drop during the annealing cycle. If too much of the day is spent annealing then there is not enough time to capture and convert radiation at the higher efficiencies. Also it is noteworthy that at operating temperatures 25 °C and 50 °C the energy generation is not maximized for the strategy of Case IV. Instead, the energy is highest for Case V (annealing twice a day), which can be attributed to the fact that degradation is more pronounced at lower temperatures and the increased number of annealing cycles per day compensates for the loss.



Fig. 3.6 Total energy generation under normal sun at operating temperature for a) 25 °C, b) 50 °C, and c) 90 °C the four cities over a year with change in number of anneals per day

Fig. 3.6 shows the total energy generation over a year (under normal sun for operating temperatures) for a) 25 $^{\circ}$ C, b) 50 $^{\circ}$ C, and c) 90 $^{\circ}$ C for the four locations as a function of the number of anneals per day. Annealing once per day generated the maximum power. The lower values of energy than the 1 sun cases can be attributed to the reduced total flux

as compared to constant 1 sun illumination. These results show that annealing once a day is sufficient to maximize electrical energy generation using spike annealing in a-Si:H PVT.

Case Study	Operating	Goldendale	San Antonio	Reno (mW-hr)	Las Vegas
	Temperature	(mW-hr)	(mW-hr)		(mW-hr)
Case-II	25 °C	1	1	1	1
	50 °C	1	1	1	1
	90 °C	1	1	1	1
Case-III	25 °C	1.176	1.175	1.175	1.182
	50 °C	1.064	1.063	1.063	1.068
	90 °C	1.009	1.007	1.007	1.009
Case-IV	25 °C	1.235	1.231	1.23	1.24
	50 °C	1.1	1.098	1.097	1.105
	90 °C	1.015	1.012	1.012	1.016
Case- V	25 °C	1.233	1.222	1.221	1.226
	50 °C	1.098	1.089	1.089	1.093
	90 °C	1.004	0.997	0.997	0.999
Case-VI	25 °C	1.221	1.205	1.205	1.207
	50 °C	1.088	1.075	1.074	1.076
	90 °C	0.993	0.983	0.982	0.983
Case-VII	25 °C	1.204	1.182	1.181	1.181
	50 °C	1.072	1.052	1.051	1.051
	90 °C	0.98	0.964	0.964	0.962
Case-VIII	25 °C	1.194	1.178	1.177	1.176
	50 °C	1.062	1.048	1.047	1.046
	90 °C	0.971	0.959	0.959	0.957

Table 3.1: Total energy generation over a year for the four cities for different case studies

Case-IX	25 °C	1.177	1.169	1.168	1.169
	50 °C	1.047	1.04	1.039	1.039
	90 °C	0.957	0.952	0.951	0.951

Table 3.1 shows the simulated normalized energy generation over a year for the four cities. All the values were normalized with respect to the no annealing energy generation at corresponding operating temperatures. Case Study-IV (annealing once per day) was found to be the most effective dispatch strategy; resulting in more than 23%, 10%, and 1.2% additional energy generation over a year for the operating temperatures 25 °C, 50 °C, and 90 °C respectively while the total energy generation is maximum for operating temperature 90 °C. These values are in agreement with past work [2] that predicted about a 10% improvement using only 1 sun degradation and daily spike anneals at 50 °C. The results also underscore the importance of using real temperatures and not STC in the optimization of PV devices. Although, using Case IV at 25 °C showed more than a 23% increase in output in most locations the operating temperatures for PV are much higher. It is also clear that running a-Si:H PV/T at high temperatures (e.g. 90 °C) negated the majority of the spike annealing benefit gaining only about 1%. At all temperatures, one time annealing per day during peak sun hours is sufficient to generate maximum power in all of the geographic locations simulated. Geographic location (at least within the contiguous United States) does not appear to be an important variable for determining the optimum dispatch strategy for the electrical output of spike annealing a-Si:H PV/T devices as the range in solar flux was not enough to appreciably effect the dispatch strategy for annealing. In general the operating temperature for solar cells can be easily raised to 50 °C, but using the thermal collector it is possible to maintain a steady temperature of 90 °C which provides even higher energy.

Now that a suitable dispatch strategy has been developed future work is needed to determine the degradation characteristics at temperatures other than 25 °C, 50 °C, and 90 °C. Using Eq. (2.3) it is possible to obtain the degradation traits at other temperatures, but the problem lies on determining the accurate values of the parameters k_{dss} and u_{dss} as

these parameters are functions of the PV/T temperature. In such a case the values can be approximated (e.g. if at temperatures T_1 and T_2 ($T_1 < T_2$) the values of parameter k_{dss} are k_{dss1} and k_{dss2} respectively, then at a temperature T_x such that $T_1 < T_x < T_2$ the value of k_{dss}) using:

$$k_{dssx} = k_{dss1} + \frac{(k_{dss2} - k_{dss1})}{(T_2 - T_1)} \times (T_x - T_1)$$
(3.1)

Similarly the equation for getting u_{dssx} is following,

$$u_{dssx} = u_{dss1} + \frac{(u_{dss2} - u_{dss1})}{(T_2 - T_1)} \times (T_x - T_1)$$
(3.2)

Using Eqs. (3.1) and (3.2) it is possible to determine the approximate values of k_{dss} and u_{dss} for an arbitrary operating temperature. Future research can focus on experiments that could help reduce the error associated with this approximation by using actual field temperatures. In addition, the positive results found in the simulations, indicate that future work should be undertaken to verify the energy gains using a-Si:H PV/T with daily annealing pulses and to find the optimal operating temperature to maximize electrical output. Finally, further work is necessary to maximize the total exergy of the system [3], by considering the effects of annealing pulses on the thermal energy recovered from the PV/T and a final optimal dispatch strategy can be determined taking into account load data for a specific application and location.

In general the outdoor temperature varies frequently over a day hence the above mentioned equations can be used in approximately determining the values of the parameters k_{dss} and u_{dss} with temperature change. This will eventually take into account the effect of temperature on solar power generation using PV/T. Chapter 4 portrays the impact of varying temperature on PV/T performance thoroughly. The dispatch mechanism in real world scenario is also analyzed in this chapter.

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CHAPTER 4

Results: Outdoor Temperature Simulation

The preceding chapters focused on the hybrid amorphous silicon solar photovoltaic thermal (PVT) system behavior associated with annealing of defect states in the PV absorber and corresponding dispatch strategies under sustained operating temperatures, showed that the degradation associated parameters varies with the operating temperature. To provide analysis for real-world conditions over which the temperature can fluctuate significantly, the effect of temperature has been incorporated in the updated model. By considering the degradation associated parameters as functions of temperature differential increment/decrement calculation is used to obtain the values of these parameters for the intermediate temperatures. In addition, the annealing associated PVT performance in real world outdoor environment scenario- where the temperature and solar irradiance varies frequently has been studied in detail.

4.1 Background[‡]

4.1.1 Degradation Associated Parameters

Previous chapter has introduced the parameters k_{dss} and u_{dss} [1] also referred as the degradation associated parameter plays a major role in rendering the degradation phenomenon. These parameters were introduced in the max power generation equation in order to modify the equation for PV/T and incorporate the effect of SWE in it [1]. It is really important to understand how their values change with temperature.

[‡] The material contained in this chapter has been submitted to the journal, *Renewable Energy*.

Exponential fits [1] to experimental data (Figure 2.2) showing degenerated steady state obtained at sustained operating temperatures 25 °C, 50 °C, and 90 °C y for a-Si:H PV cell active layer thickness of 630 nm under 1 sun (source: Pathak et. al.) [2] were used to derive k_{dss} and u_{dss} .

When the irradiance is constant, it is notable that the exponential degradation rate and the final degenerative steady state power generation both depend on the operating temperature. To take into account the effect of operating temperature outside of fixed values the degradation rate and the steady state power generation is required to make a function of temperature. In other words, the degradation associated parameters k_{dss} and u_{dss} should be represented as a function of temperature. The parameter k_{dss} explains the degenerative steady state and u_{dss} justifies the degradation rate. It has also been observed that k_{dss} decreases and u_{dss} increases with temperature rise. Another remarkable observation is that at higher temperature power generation reaches steady state with a faster degradation rate (requires less time) while it is opposite for the lower temperature cases. Also steady state power generation is higher at higher temperatures. Equation (3.1) and (3.2) linearly calculate the values of these parameters in the intermediate regions between 25 °C to 50 °C and 50 °C to 90 °C [1]. Figure 4.1 and 4.2 shows the corresponding plots.



Fig. 4.1 Degradation associated parameter k_{dss} against temperature



Fig. 4.2 Degradation associated parameter u_{dss} against temperature

As a first approximation the changes in the parameter values have been considered to be changing linearly in the range between the experimentally measured temperatures. Hence, there exist two linear regions with different slopes in each plot. The value of the parameters outside the range of 25 °C to 90 °C is calculated by extending the lines linearly.

4.2 Methodology

4.2.1 Global Expansion and Simulation Mechanism Updates

Previous simulations were confined to four specific cities in United States [1]. In order to expand the optimization maps for the performance of the PV/T it is required to expand the modeling range by including more solar data collected from worldwide solar resources and satellites. As a primary approach in the present work the solar data for regions all over US (including Alaska and Hawaii) and Western Canada has been included in the simulation. Primarily the hourly solar irradiance and temperature data from the U.S. air force weather stations has been used [3, 4]. The NREL Solar Prospector has been utilized as well for collecting the solar data in US using geographic coordinates [5]. The Canadian data was obtained from the National Resources Canada (NRCAN) website [6]. The simulation mechanism is almost similar as before except the fact that the

user has the freedom to access more data from around all over U.S. and Western Canada. Users can input solar data in the simulation using either known USAF station ID or geographic coordinates and the program gives the exact PV/T output at different operating conditions and dispatch strategies. Also it is notable that the hourly outdoor temperature data has been utilized in the simulation hence the degradation associated parameters k_{dss} and u_{dss} fluctuates in accordance with the temperature. The solar data that has been utilized is the METSTAT-modeled global horizontal solar irradiation data [7] which indicates the total amount of direct and diffuse solar radiation (METSTAT-modeled) received on a horizontal surface during the 60-minute period ending at the timestamp.

4.2.2 Association of Temperature Data for Selected Locations

For better understanding of the PVT behavior it is required to include the hourly temperature time series data. For a particular location the temperature varies frequently. In the same manner the degradation associated parameters vary hourly. The analysis utilizes time series temperature data along with the hourly solar irradiance data for four particular locations with different atmospheric condition. These locations were chosen according to the incidence of solar flux and temperature readings. The approach was to include locations with four different atmospheric criteria:

- 1. High solar flux/high temperature
- 2. High solar flux/low temperature
- 3. Low solar flux/high temperature
- 4. Low solar flux/low temperature

As for the first standard the city of Casa Grande, Arizona was chosen where the flux and temperature is fairly high all through the year. For the second category city of Aspen in Pitkin County, Colorado is chosen where the temperature is very low while the corresponding solar flux is surprisingly high. For the third category city of Apalachicola, Florida was chosen where the temperature is very high regardless the fact that the area gets comparatively less solar flux. Finally, city of Anchorage in Alaska was chosen for the fourth category. Here it is to be mentioned that usually the amount of incidence of solar flux depends on the geographic coordinate, incident angle and air mass/optical path of incidence. On the other hand, the temperature mostly depends on the humidity and air mass. In general the average hourly solar flux in Aspen, Colorado (193.83 W/m²) is lower than Apalachicola, Florida (214.97 W/m²) but the average hourly temperature in Aspen, Colorado (5.23 °C) is very low regardless the fact they get a decent amount of solar flux. Hence, Aspen has been chosen as a high solar flux/low temperature area. On the other hand the temperature in Apalachicola, Florida (20.4 °C) is remarkably high for a moderate incident flux. Thus Apalachicola is chosen as a low flux/high temperature area. Table 4.1 shows the chosen locations based on flux/ temperature readings.

 Table 4.1: Chosen cities based on atmospheric criteria

	High Flux	Low Flux
High Temperature	Casa Grande, Arizona	Apalachicola, Florida
Low Tempearature	Aspen, Colorado	Anchorage, Alaska

Table 4.2 shows the summary of climates for the chosen cities. The time series hourly data sets starting from January 1st, 2002 to December 31st, 2002 were utilized in the simulation. It is to be noted that the average hourly temperature in this cities are lower than 25 °C which was the lowest operating temperature in the consistent operating temperature PVT dispatch model.

 Table 4.2 Summary of climate of the chosen cities

City	Coordinates	Average Hourly Temperature (for the year 2002)	Altitude	Average hourly solar irradiance (for the year
------	-------------	--	----------	--

				2002)
Anchorage (Anchorage Borough, Alaska)	61.2167° N, 149.9000° W	-3.44598 °C	102 ft.	100.7629 W/m ²
Casa Grande (Pinal County, Arizona)	32.8858° N, 111.7439° W	21.59384 °C	1,398 ft.	251.3572 W/m ²
Apalachicola (Franklin County, Florida)	29.7253° N, 84.9925° W	20.39634 °C	13 ft.	214.9726 W/m ²
Aspen (Pitkin County, Colorado)	39.1922° N, 106.8244° W	5.232163 °C	7,890 ft.	193.8292 W/m ²

Figure 4.3 and 4.4 shows the daily average solar flux and the temperature reading in the four chosen cities. Average solar irradiance per day for the cities (Anchorage, Casa Grande, Apalachicola, and Aspen) are 2.42, 6.03, 5.16, and 4.65 sun hours respectively. The peak sun hour with high flux lies in between 900 to 1600 hrs when the flux is higher than 250 W/m². Also it is noteworthy that during these hours the temperature is comparatively low which means the degradation occurs at a slow rate.



Fig 4.3 Average hourly solar irradiation per day for the four cities



Fig. 4.4 Average hourly temperature readings per day for the four cities

4.3 Results

4.3.1 Simulation at Sustained Operating Temperature

As an initial step of the analysis the simulation was performed at sustained operating temperatures where the degradation parameters are constant. Figure 4.5, 4.6, 4.7 and 4.8 shows the output obtained for the sustained operating temperature simulation in the four representative cities. In all the cases the 90 °C operating temperature with 1 time annealing per day provides the maximum power output.



Fig. 4.5 Total electrical energy generation over a year under different annealing conditions in Anchorage, AK at sustained operating temperatures



Fig. 4.6 Total electrical energy generation over a year under different annealing conditions in Casa Grande, AZ at sustained operating temperatures



Fig. 4.7 Total electrical energy generation over a year under different annealing conditions in Apalachicola, FL at sustained operating temperatures



Fig. 4.8 Total electrical energy generation over a year under different annealing conditions in Aspen, CO at sustained operating temperatures

Figure 4.9 shows the maximum electrical energy generation for the four cities at sustained operating temperatures. Table 4.3 shows the normalized max energy obtained for the sustained operating temperature cases.



Fig. 4.9 Maximum electrical energy generation (obtained for annealing one time every day) over a year in the four cities at sustained operating temperatures

 Table 4.3 Normalized max electrical energy generation with respect to 25 °C max

 energy at sustained operating temperatures (anneal cycle: once every day)

	Normalized Max	Normalized Max	Normalized Max		
Cities	Electrical Energy	Electrical Energy	Electrical Energy at		
	at 25 °C	at 50 °C	90 °C		
Anchorage, AK	1	1.0025	1.0130		
Casa Grande, AZ	1	1.0019	1.0088		
Apalachicola, FL	1	1.0017	1.0087		
Aspen, Colorado	1	1.0076	1.0103		

The results of the sustained operating temperature simulation are pretty straight forward and comply with the fact that energy generation is higher at 90 $^{\circ}$ C.

4.3.2 Sensitivity and Outdoor Operating Conditions

The outdoor temperature performance of PV/T is distinctly complicated. For the performance analysis an environmental insulation based sensitivity study is carried out. Four cases of outdoor operating conditions are included in the study. Table 4.4 shows the list of case studies.

Cases	Operating Temperature
Case I	90 °C (Sustained with high insulation)
Case II	Outdoor Temperature (no insulation)
Case III	Outdoor Temperature+25 °C (low insulation)
Case IV	Outdoor Temperature+50 °C (med. insulation)

 Table 4.4 List of case studies for outdoor operating temperature

In Case I the PVT is considered to be highly insulated and maintains a constant operating temperature 90 °C. 90 °C was chosen as the operating temperature as the panels

generate more power at this temperature compared to 25 °C and 50 °C because of the annealing effects of the higher temperature on defect state density. In Case II the PVT panels are not insulated at all and operate at outdoor temperature. In Case III the PVT panels are considered to be insulated in such a way so that the operating temperature is higher than the outdoor temperature by 25 °C. Case IV operating condition is similar to Case III except the fact that the panels are insulated better and operating temperature is higher than the outdoor temperature by 50 °C. Figure 4.10 shows the sensitivity plot for all the outdoor operating temperature case studies.



Fig. 4.10 Sensitivity study with different outdoor operating conditions

4.3.3 Simulation at Outdoor Operating Conditions

Outdoor simulations were performed by taking into account the outdoor operating case studies along with the anneal cycle case studies from previous work [1]. Figure 4.11, 4.12, 4.13 and 4.14 shows the overall electrical energy generation for the representative cities at outdoor operating conditions. From the figures it can be seen that in each area the panels generate more power when operated at outdoor temperatures which is on average lower than 25 °C in each city. Along with the outdoor operating conditions the different annealing cycle cases starting from no anneal to 6 times anneal per day are studied in the present simulation.

In Anchorage, AK (Figure 4.11) the effect of annealing is very minor and eventually causes a power drop while operation without annealing gives the maximum power. This behavior can be attributed to the fact that the temperature is very low in Alaska (-3.44598 °C on average) and at low temperatures the initial degradation rate is very small, although the DSS is worse than for higher temperatures. Also the initial drop in the power during annealing is more significant compared to the after anneal power increase. This introduces more power loss rather than compensating for the light induced degradation. Thus rapid annealing cycles, which themselves have parasitic losses do not generate additional electrical energy. In such a case it is more suitable to reduce the frequency of annealing cycles. This is discussed in detail in the latter section.



Fig. 4.11 Total electrical energy generation over a year under different annealing cycles in Anchorage, AK at outdoor operating conditions

In Casa Grande, AZ (Figure 4.12) the flux and temperature are comparatively very high. The simulation shows power generation is better at outdoor operating temperatures than the other sensitivity controlled outdoor operating conditions. Maximum power is generated with the anneal frequency five times per day. It is similar in case of Apalachicola, FL (Figure 4.13) as well except the fact that the anneal frequency is six times per day. Such requirements of high number of anneals per day in Casa Grande and Apalachicola refers to the fact that the degradation is more rapid in locations with higher

outdoor temperature and more anneal pulses are required to compensate for this power loss due to fast states [8, 9]. It is also true that anneal pulses are accompanied with an initial power drop but compared to the SWE degradation and after anneal rapid power boost this drop is minor. In Aspen, CO (Figure 4.14) the outdoor temperature is low for a reasonable amount of incident solar flux in this region. Simulation result shows that one time annealing everyday at outdoor operating temperature is good enough for maximum power generation.



Fig. 4.12 Total electrical energy generation over a year under different annealing cycles in Casa Grande, AZ at outdoor operating conditions



Fig. 4.13 Total electrical energy generation over a year under different annealing cycles in Apalachicola, FL at outdoor operating conditions



Fig. 4.14 Total electrical energy generation over a year under different annealing cycles in Aspen, CO at outdoor operating conditions

Figure 4.15 shows the max energy output for all the four cities and includes data for both the sustained operating temperature cases and outdoor operating temperature cases. In all the locations the outdoor operating temperature yield the maximum output. The max energy obtained at Aspen, CO is close to the max energy obtained at Apalachicola, FL regardless the fact that Florida gets more solar flux than Colorado. This can be attributed to the degradation rate stagnating at locations with lower outdoor temperatures. In Colorado, for example, the net electrical energy generation without annealing is higher than Florida. In Florida the flux is high, but the temperature is relatively high as well, which results in rapid degradation hence the net energy generation without annealing is lower. On the other hand additional power generation due to annealing is more in Florida compared to Colorado. This is because of the rapid degradation of generated power in Florida, which makes more room for the anneal pulses to take place and produce more annealing-associated additional electrical energy.



Fig. 4.15 Maximum electrical energy generation over a year for the four cities at sustained temperature (anneal cycle is one time per day) and outdoor operating conditions (anneal cycle varies from one place to another)

Table 4.5 shows the summary of the outdoor operating condition simulation. The data represents the output electrical energy at operating temperature same as the outdoor temperature. It contains the max energy obtained for the four cities when annealing is applied. The additional energy generated due to annealing is also shown.

Table 4.5 Max	electrical energy	generation	over a	year in	i the lour	cities at	outdoor
operating temperatur	re						

. 1

Cities	Max Electrical Energy Without Annealing (kW-hr)	Max Electrical Energy With Annealing (kW-hr)	Required Number of Anneals	Additional energy Generation (%)
Anchorage, AK	0.0046	0.00457	Once every other day	-6.52 %
Casa Grande, AZ	0.00737	0.0099	5 times/day	34.35 %
Apalachicola, FL	0.0063	0.00838	6times/day	33.17 %
Aspen, CO 0.0068 0.00834 1 time/day 22.47 9	0			
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The following are the observations that summarize the whole section:

- 1. Outdoor operating temperature provides the maximum energy in all the representative climate cities.
- 2. Annealing frequency should be changed from one location to another depending on the outdoor temperature and incident solar flux
- 3. Effect of annealing is significant in locations with higher outdoor temperatures. The additional energy generation due to annealing is higher in Casa Grande, AZ (34.35%) and Apalachicola, FL (33.17%) where the outdoor temperature is higher on average. Also the annealing frequency is high for generation of this amount of additional power. For Casa Grande the anneal frequency is five times per day and for Apalachicola it is six times per day. In other words, annealing associated additional energy generation is higher in places with higher temperature.
- 4. Max energy generation (without annealing at outdoor operating temperatures) is higher in regions with lower outdoor temperatures. As for example, Aspen, CO gets lower flux compared to Apalachicola, FL yet generates more power than Apalachicola without annealing (as per Table 4.5). This can be attributed to the lower outdoor temperature in Aspen which stagnates the power degradation rate.
- 5. In locations with extremely low temperatures, the effect of annealing is minor and a-Si:H PVT panels do not necessarily generate additional electrical energy under rapid annealing cycles. On the other hand, the maximum electrical energy without annealing is high. As for example, the additional energy generation due to annealing (once every other day) in Anchorage, AK is -6.52 %, which represents an electrical energy loss.

4.3.4 Appropriate Dispatch Strategy

The preceding sections ascertained that annealing contribute to additional electrical energy generation in PVT. But annealing is also accompanied with PVT panel thermal energy consumption. Hence it is necessary to optimize the annealing cycle and obtain the most effective dispatch strategy for the total energy. This is left for future work, which should use exergy to determine the optimal routine. A sensitization was perfomed on following bases:

- 1. Depending on the climate features of any particular region dispatch strategy should be adapted
- 2. The frequency of annealing should be as low as possible- reduces the annealing associated thermal energy consumption
- 3. The energy generation should be as high as possible and must be close to max energy generation

The dispatch strategy reasoning for each city is discussed in detail in following segments.

a) Anchorage (Alaska): The outdoor operating temperature simulation result shows that max power in Anchorage was obtained without annealing and rapid annealing reduces power generation. The power degradation rate is very low due to extremely low outdoor temperature. Hence it is required to reduce the frequency of annealing cycles to obtain power greater than the no anneal situation. Using the rules above, annealing only once in a year (approximately after 8640 hours) was chosen to be an ideal strategy for this city. It resulted in generation of .000345 % additional energy which is very negligible. Further reduction of annealing frequency i.e. annealing once in every two years will possibly provide additional energy.

- b) Casa Grande (Arizona): In Casa Grande the max energy was obtained for the strategy that consists of five times annealing everyday at outdoor operating temperature. In Table 4.5 an additional energy of 34.35 % is reported for this strategy. It has also been observed that one time annealing per day generates 33.45 % additional energy which is fairly close to the energy generation with five times anneal per day. This will also reduce the annealing associated heating energy consumption. Thus annealing once every day should be a good compromise dispatch strategy for Casa Grande.
- c) Apalachicola (Florida): In Apalachicola the max energy was obtained for a dispatch strategy consisting six times annealing per day- resulted in 33.17% additional energy generation. If the anneal cycle is reduced to one time every day 29.33% additional electrical energy generation is still generated, while cutting the annealing associated heating energy consumption down by a factor of six. This compares to the exergy for PV being higher than solar thermal for PV systems by a factor of six.
- d) Aspen (Colorado): According to Table 4.5, the maximum energy for Aspen was obtained for the strategy- one time anneal every day. This strategy is also likely to provide a favorable dispatch strategy for Aspen with 22.47 % additional electrical energy generation.

Table 4.6 shows comparison of the dispatch strategies that give the maximum electrical energy with the strategies that gives favorable PVT performance. The calculation only involves electrical energy generation and hence it is not the optimized one. The appropriate dispatch strategy in this case can be defined as the strategy that generates electrical energy close to max possible electrical energy with lower frequency of anneal cycles. Similarly max energy dispatch strategy refers to the strategy that generates maximum electrical energy.

Cities	Max Energy Without Anneali ng (kW- hr)	Max Electrical Energy Dispatch Strategy		Appropriate Dispatch Strategy					
		Generated Electrical Energy (kW-hr)	Required Number of Anneals	Additional energy Generation (%)	Generated Electrical Energy (kW- hr)	Required Number of Anneals	Additiona l energy Generatio n (%)	Advantage	Draw backs
Anchorag e, AK	0.004592 592	0.00459259 2	No Anneal	0 %	0.004592608 7	Once every year	.000345%	Energy generation increased	N/A
Casa Grande, AZ	0.00737	0.0099	5 times/day	34.35 %	0.009843	1 time/day	33.45%	Reduces annealing associated energy consumption	Energy generatio n decreased
Apalachic ola, FL	0.0063	0.00838	6times/day	33.17 %	0.008148	1 time/day	29.33%	Reduces annealing associated energy consumption	Energy generatio n decreased
Aspen, CO	0.0068	0.00834	1 time/day	22.47 %	0.00834	1 time/day	22.47 %	N/A	N/A

Table 4.6 Comparison between max electrical energy dispatch strategies and appropriate strategies

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CHAPTER 5

Discussion, Future Work and Conclusions

Amorphous silicon based solar cells have a lower thermal coefficient than c-Si, but their performance is undermined by the fact that long time light exposure causes formation of defect states that reduces power generation. Fortunately, a-Si:H also has the ability to reduce the quantity of defect states with exposure to high temperature annealing pulses. This property makes them more suitable for PV/T applications where the thermal collector temperature can be easily raised to the annealing temperature. Yet suitable dispatch strategies are prerequisite to obtain the optimal benefits of the PV/T assembly. Earlier chapters sum up the investigation methodologies and results of variant dispatch schemes. This chapter contains the discussions including the consistency of the simulation, limitations of the present method, improvements and the future works.

5.1 Discussions

5.1.1 Consistency of Simulation

The consistency of the simulation determines how accurate results are obtained. In the current method of outdoor environment operation of PVT it has been considered that the panels operate at outdoor temperature. In reality the temperature of the PVT panels get higher than the outdoor temperature which eventually affects the PVT degradation behavior and also the PVT panel output. It is really hard to obtain accurate panel temperature from theory as heat is transferred mostly through conduction mechanism and there exist temperature gradient between each component in the module. Both experimental and theoretical studies of thermal conductance and heat transfer in a-Si:H is required to perform for better understanding of the phenomenon.

5.1.2 Limitations of the Simulation Method

One of the major drawbacks of the model is the accuracy of values of the degradation associated constants k_{dss} and u_{dss} . These values were calculated linearly from the plots shown in Figure 4.1 and 4.2. Also the values of the parameters outside the 25 °C-90 °C range were calculated by extending the line on both sides. The technique is not very efficient. As the number of basic data points were limited to three it was not possible to obtain an accurate fitting. Given more data points of k_{dss} and u_{dss} values in between the range 25 °C to 90 °C it will be possible to come up with a more accurate fitting curve for k_{dss} and u_{dss} . The range of experimental data must include the 1 sun PV/T degradation plots below 25 °C (e.g. -10 °C to 25 °C) as that range of temperature is more favorable for PV/T operation.

Another limitation of the degradation associated parameters is their value limits. The value of u_{dss} falls with decrease in temperature and after certain temperature (approximately 2 °C) the value of u_{dss} becomes negative. Theoretically it is not possible for u_{dss} to obtain negative value because that refers to rise in power rather than degradation. Thus when u_{dss} value is below 0 the value is set to 0. Similarly the max limit for k_{dss} value is 0.4642 and the parameter value cannot exceed the limit. Exceeding the limit deteriorates degradation behavior.

From the study of PV/T performance and dispatch strategy in Alaska it was found that annealing has very minor impact on additional power generation in this region. Annealing only one time in a year resulted in a negligible amount of additional energy generation (.000345%). It is possible that annealing only once in two or three years may yield higher additional energy generation. Due to limited access to data it was not possible to effectively optimize the situation.

The calculation of appropriate dispatch strategy does not include the thermal energy consumption associated with annealing and hence is not optimized. This portion of energy is a part of the energy loss and may change the energy output at a high margin and needs to be investigated in the future. Also due to the limitation of access to required data and insufficiency of resources it was not possible to gather the data from all around the world. With more availability of global data better understanding of PVT behavior is possible.

5.2 Future Work

This study broadened the future scope of research in the field of a-Si:H PVT dispatch strategy and annealing. One of the more highlighted topics will be fitting the degradation associated parameter curves more accurately using experimental values. In addition, more detailed studies of snow and its impact on solar energy devices [1] such as PVT performance can provide insight into the dispatch strategies and annealing cycles in snowbound areas. Moreover, using PV/T trade-off between the thermal power and electric power is possible upon users demand. In other words, tunability between the thermal and electric power is possible. This will give users more flexibility on usage of PVT and they can set the PVT operating condition upon their instant demand of thermal power or electric power. Studies of the temperature/annealing controller aided automatic generation of anneal sequence as a function of outdoor temperature and flux will make the whole system more useful and practical for global application. Finally mathematical computation of thermal energy consumption due to spike annealing could be a good topic for experimental research.

5.3 Conclusion

The results of the initial study (Chapter 3), investigated the impact of annealing cycles and geographic locations with real solar flux data showed that at standard and sustained PV operating temperatures one anneal pulse per day provided the largest electrical output through the year. The results showed that significant amount of additional energy generation is possible over the year with an appropriate dispatch strategy and operating temperature providing 23%, 10%, and 1.2% additional energy generation over a year for the operating temperatures 25 °C, 50 °C, and 90 °C respectively. The outcome inclined that further study of annealing cycles and analysis of the degradation at other operating temperatures coupled with the optimization of the

thermal component of the PV/T can provide the optimal dispatch strategy for the devices for any application.

The latter part of the study (Chapter 4) is an expansion of the earlier work aimed to diagnose the real world outdoor environment performance of PVT under application of annealing cycles. The study includes solar data from all over U.S. and Canada. The main feature of the model is that it expands the limits of operation from sustained operating temperatures to outdoor operating temperature. The result of simulation reports the impact of annealing and maximum possible energy outputs at different outdoor operating conditions. It was found that compared to sustained temperatures. Finally, a logical approach was taken to optimize the dispatch strategies which hold limitations with the accurate reckoning of the associated exergy and thermal energy. The present work concludes with the notion that with access to required data and considering the bases of sensitization as the rule of thumb it is possible to implement suitable dispatch strategies and execute virtual performance analysis of PV/T for any places around the world.

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Appendix I

Program Code: Ideal Cases

```
% load data files
load T630nm_25c.mat
load T630nm 50c.mat
load T630nm 90c.mat
load T630nm 25c new.mat
load T630nm 50c new.mat
load T630nm 90c new.mat
load Goldendale_168.mat
load San Antonio 168.mat
load Reno 168.mat
load Vegas 168.mat
load Goldendale 366.mat
load San Antonio 3661.mat
load Reno 3661.mat
load Vegas_3661.mat
load t1 caseVII.mat
load t1 caseVIII.mat
load t1 caseIX.mat
load t1 caseX.mat
load t1 caseXI.mat
load t1 caseXII.mat
load t1 caseXIII.mat
load x25.mat
load x50.mat
load x90.mat
load y25.mat
load y50.mat
load y90.mat
load counter_caseVII.mat
load counter_caseVIII.mat
load counter caseIX.mat
load counter caseX.mat
load counter caseXI.mat
load counter caseXII.mat
load counter caseXIII.mat
load counter_caseVII_366.mat
load counter_caseVIII_366.mat
load counter caseIX 366.mat
load counter caseX 366.mat
load counter caseXI 366.mat
load counter caseXII 366.mat
load counter caseXIII 366.mat
% Solar irradiance for the four cities
plot(t(1,1:25),Goldendale 168(1:25,1),'k');
hold on
plot(t(1,1:25),San Antonio 168(1:25,1));
hold on
```

```
plot(t(1,1:25),Reno 168(1:25,1),'g');
hold on
plot(t(1,1:25), Vegas 168(1:25,1), 'r');
hold on
% constants
delta=0.063;
gamma=-0.002;
% pref=5.526;
pref=5.2825;
T 25=273+25;
T 50=273+50;
T 90=273+90;
T ref=273+25;
% t =[0:192];
% t =[0:600];
t=[0:8783];
% u25=0.05205;
u25=0.03601;
% u50=0.1293;
u50=0.07552;
u90=0.2097;
% kdss25=0.3276;
kdss25=0.3450;
% kdss50=0.2023;
kdss50=0.2154;
kdss90=0.07917;
% original data
% plot(T630nm 25c new(1:539,1),mat2gray(T630nm 25c new(1:539,2),[0
5.278]), 'g')
% hold on
% plot(T630nm 50c new(1:545,1),mat2gray(T630nm 50c new(1:545,2),[0
5.278]))
% hold on
% plot(T630nm 90c new(1:383,1),mat2gray(T630nm 90c new(1:383,2),[0
5.278]), 'r')
% hold on
% plot(x25,mat2gray(y25,[0 5.278]),'g')
% hold on
% plot(x50,mat2gray(y50,[0 5.278]))
% hold on
% plot(x90,mat2gray(y90,[0 5.278]),'r')
% hold on
% case-I: under 1 sun without annealing
pmax 50=pref/(1+gamma*(T ref-T 50));
pmax 90=pref/(1+gamma*(T ref-T 90));
tpDSS 90=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-u90)*t));
```

```
tpDSS 50=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-u50)*t));
tpDSS 25=pref-(kdss25*pref)*(1-exp((-u25)*t));
pDSS_90=tpDSS_90.';
pDSS 50=tpDSS 50.';
pDSS 25=tpDSS 25.';
% figure
% plot(t,mat2gray(pDSS 25,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pDSS 50,[0 5.278]))
% hold on
% plot(t,mat2gray(pDSS 90,[0 5.278]),'r')
% case-V: under normal sun without aneealing
%
pmax 25 caseV sa=(pDSS 25).*((San Antonio 168).*(1./(1+delta*(log(1./Sa
n Antonio 168)))));
pmax 25 caseV re=(pDSS 25).*((Reno 168).*(1./(1+delta*(log(1./Reno 168)
))));
0/0
pmax 25 caseV ve=(pDSS 25).*((Vegas 168).*(1./(1+delta*(log(1./Vegas 16
8)))));
2
pmax 25 caseV gd=(pDSS 25).*((Goldendale 168).*(1./(1+delta*(log(1./Gol
dendale 168)))));
pmax_50_caseV_sa=(pDSS_50).*((San_Antonio_168).*(1./(1+delta*(log(1./Sa
n Antonio 168)))));
00
pmax 50 caseV re=(pDSS 50).*((Reno 168).*(1./(1+delta*(log(1./Reno 168)
))));
pmax 50 caseV ve=(pDSS 50).*((Vegas 168).*(1./(1+delta*(log(1./Vegas 16
8)))));
%
pmax 50 caseV gd=(pDSS 50).*((Goldendale 168).*(1./(1+delta*(log(1./Gol
dendale 168)))));
pmax_90_caseVI_sa=(pDSS_90).*((San_Antonio_168).*(1./(1+delta*(log(1./S
an Antonio 168)))));
8
pmax 90 caseVI re=(pDSS 90).*((Reno 168).*(1./(1+delta*(log(1./Reno 168
)))));
2
pmax 90 caseVI ve=(pDSS 90).*((Vegas 168).*(1./(1+delta*(log(1./Vegas 1
68)))));
pmax 90 caseVI gd=(pDSS 90).*((Goldendale 168).*(1./(1+delta*(log(1./Go
ldendale 168)))));
% figure
% plot(t,mat2gray(pmax 25 caseV gd,[0 5.278]),'k')
% hold on
% plot(t,mat2gray(pmax 25 caseV sa,[0 5.278]))
```

```
% hold on
% plot(t,mat2gray(pmax 25 caseV re,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pmax 25 caseV ve,[0 5.278]),'r')
% hold on
% figure
% plot(t,mat2gray(pmax 50 caseV gd,[0 5.278]),'k')
% hold on
% plot(t,mat2gray(pmax 50 caseV sa,[0 5.278]))
% hold on
% plot(t,mat2gray(pmax 50 caseV re,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pmax 50 caseV ve,[0 5.278]),'r')
% hold on
% figure
% plot(t,mat2gray(pmax 90 caseVI gd,[0 5.278]),'k')
% hold on
% plot(t,mat2gray(pmax 90 caseVI sa,[0 5.278]))
% hold on
% plot(t,mat2gray(pmax 90 caseVI re,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pmax 90 caseVI ve,[0 5.278]),'r')
% hold on
pmax 25 caseV sa 366=(pDSS 25).*((San Antonio 3661).*(1./(1+delta*(log(
1./San Antonio 3661)))));
pmax 25 caseV re 366=(pDSS 25).*((Reno 3661).*(1./(1+delta*(log(1./Reno
3661)))));
pmax 25 caseV ve 366=(pDSS 25).*((Vegas 3661).*(1./(1+delta*(log(1./Veg
as 3661)))));
pmax_25_caseV_gd_366=(pDSS_25).*((Goldendale 366).*(1./(1+delta*(log(1.
/Goldendale 366))));
pmax_50_caseV_sa_366=(pDSS_50).*((San_Antonio_3661).*(1./(1+delta*(log(
1./San Antonio 3661))));
pmax 50 caseV re 366=(pDSS 50).*((Reno 3661).*(1./(1+delta*(log(1./Reno
3661)))));
pmax 50 caseV ve 366=(pDSS 50).*((Vegas 3661).*(1./(1+delta*(log(1./Veg
as 3661)))));
pmax 50 caseV gd 366=(pDSS 50).*((Goldendale 366).*(1./(1+delta*(log(1.
/Goldendale 366)))));
pmax 90 caseVI sa 366=(pDSS 90).*((San Antonio 3661).*(1./(1+delta*(log
(1./San_Antonio 3661)))));
pmax 90 caseVI re 366=(pDSS 90).*((Reno 3661).*(1./(1+delta*(log(1./Ren
o 3661)))));
pmax 90 caseVI ve 366=(pDSS 90).*((Vegas 3661).*(1./(1+delta*(log(1./Ve
gas 3661)))));
pmax 90 caseVI gd 366=(pDSS 90).*((Goldendale 366).*(1./(1+delta*(log(1
./Goldendale 366)))));
% case-X: annealing once per 2 days
% j=1;
% for i=1:193 % operating temp 90C
      if counter caseX(i) == 1
8
      tpDSS 90 X(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
8
u90)*t(j)));
```

```
90
      j=j+1;
90
      elseif counter caseX(i) == 2
      tpDSS_90_X(i)=.83*tpDSS 90 X(i-1);
9
9
      else
9
      tpDSS 90 X(i)=.946*pref/(1+gamma*(T ref-T 90));
9
      j=6;
90
      end
% end
% % figure
% % plot(t,mat2gray(pDSS 90,[0 5.278]),'r')
% % hold on
% % plot(mat2gray(tpDSS 90 X,[0 5.278]))
% % hold on
%
pmax 90 caseX sa=(tpDSS 90 X').*((San Antonio 168).*(1./(1+delta*(log(1
./San Antonio 168)))));
2
pmax 90 caseX re=(tpDSS 90 X').*((Reno 168).*(1./(1+delta*(log(1./Reno
168)))));
00
pmax 90 caseX ve=(tpDSS 90 X').*((Vegas 168).*(1./(1+delta*(log(1./Vega
s 168)))));
%
pmax 90 caseX gd=(tpDSS 90 X').*((Goldendale 168).*(1./(1+delta*(log(1.
/Goldendale 168)))));
% figure
% plot(t,mat2gray(pmax 90 caseX gd,[0 5.278]),'k')
% hold on
% plot(t,mat2gray(pmax 90 caseX sa,[0 5.278]))
% hold on
% plot(t,mat2gray(pmax 90 caseX re,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pmax 90 caseX ve,[0 5.278]),'r')
% hold on
j=1;
for i=1:8784 % operating temp 25C
    if counter caseX 366(i) == 1
    tpDSS 25 X(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
u25)*t(j)));
    j=j+1;
    elseif counter caseX 366(i) == 2
    tpDSS 25 X(i)=.83*tpDSS 25 X(i-1);
    else
    tpDSS 25 X(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 X(1,1:192),[0 5.278]))
```

```
% hold on
pmax 25 caseX sa 366=(tpDSS 25 X').*((San Antonio 3661).*(1./(1+delta*(
log(1./San Antonio 3661)))));
pmax 25 caseX re 366=(tpDSS 25 X').*((Reno 3661).*(1./(1+delta*(log(1./
Reno 3661)))));
pmax 25 caseX ve 366=(tpDSS 25 X').*((Vegas 3661).*(1./(1+delta*(log(1.
/Vegas 3661)))));
pmax 25 caseX gd 366=(tpDSS 25 X').*((Goldendale 366).*(1./(1+delta*(lo
g(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 50C
    if counter caseX 366(i) == 1
    tpDSS 50 X(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
u50)*t(j)));
    j=j+1;
    elseif counter caseX 366(i) == 2
    tpDSS 50 X(i)=.83*tpDSS 50 X(i-1);
    else
    tpDSS 50 X(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 X(1,1:192),[0 5.278]))
% hold on
pmax 50 caseX sa 366=(tpDSS 50 X').*((San Antonio 3661).*(1./(1+delta*(
log(1./San Antonio 3661))));
pmax 50 caseX re 366=(tpDSS 50 X').*((Reno 3661).*(1./(1+delta*(log(1./
Reno 3661))));
pmax 50 caseX ve 366=(tpDSS 50 X').*((Vegas 3661).*(1./(1+delta*(log(1.
/Vegas 3661)))));
pmax 50 caseX gd 366=(tpDSS 50 X').*((Goldendale 366).*(1./(1+delta*(lo
g(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseX 366(i) == 1
    tpDSS 90 X(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
u90)*t(j)));
    j=j+1;
    elseif counter caseX 366(i) == 2
    tpDSS 90 X(i)=.83*tpDSS 90 X(i-1);
    else
    tpDSS 90 X(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
```

```
% plot(t(1,1:192),mat2gray(pDSS_90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS_90_X(1,1:192),[0 5.278]))
% hold on
pmax_90_caseX_sa_366=(tpDSS_90_X').*((San_Antonio_3661).*(1./(1+delta*(
log(1./San_Antonio_3661)))));
pmax_90_caseX_re_366=(tpDSS_90_X').*((Reno_3661).*(1./(1+delta*(log(1./
Reno_3661)))));
pmax_90_caseX_ve_366=(tpDSS_90_X').*((Vegas_3661).*(1./(1+delta*(log(1./
Vegas_3661)))));
pmax_90_caseX_gd_366=(tpDSS_90_X').*((Goldendale_366).*(1./(1+delta*(log(1./
Pmax_90_caseX_gd_366)))));
```

```
% case-IX: annealing once per day
% j=1;
% for i=1:193 % operating temp 90C
      if counter caseIX(i) == 1
8
00
      tpDSS_90_IX(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-
exp((-u90)*t(j)));
00
      j=j+1;
00
      elseif counter caseIX(i) == 2
      tpDSS 90 IX(i)=.83*tpDSS 90 IX(i-1);
0
90
      else
90
      tpDSS 90 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
      j=6;
8
9
      end
% end
% % figure
% % plot(t,mat2gray(pDSS 90,[0 5.278]),'r')
% % hold on
% % plot(mat2gray(tpDSS 90 IX,[0 5.278]))
% % hold on
9
pmax 90 caseIX sa=(tpDSS 90 IX').*((San Antonio 168).*(1./(1+delta*(log
(1./San Antonio 168)))));
2
pmax 90 caseIX re=(tpDSS 90 IX').*((Reno 168).*(1./(1+delta*(log(1./Ren
o_168)))));
8
pmax 90 caseIX ve=(tpDSS 90 IX').*((Vegas 168).*(1./(1+delta*(log(1./Ve
gas 168)))));
pmax 90 caseIX gd=(tpDSS 90 IX').*((Goldendale 168).*(1./(1+delta*(log(
1./Goldendale 168)))));
% % figure
% % plot(t,mat2gray(pmax 90 caseIX gd,[0 5.278]),'k')
% % hold on
% % plot(t,mat2gray(pmax 90 caseIX sa,[0 5.278]))
% % hold on
% % plot(t,mat2gray(pmax 90 caseIX re,[0 5.278]),'g')
% % hold on
% % plot(t,mat2gray(pmax 90 caseIX ve,[0 5.278]),'r')
```

```
% % hold on
i=1;
for i=1:8784 % operating temp 25C
    if counter caseIX 366(i) == 1
    tpDSS 25 IX(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
u25)*t(j)));
    j=j+1;
    elseif counter caseIX 366(i) == 2
    tpDSS 25 IX(i)=.83*tpDSS 25 IX(i-1);
    else
    tpDSS 25 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 IX(1,1:192),[0 5.278]))
% hold on
pmax 25 caseIX sa 366=(tpDSS 25 IX').*((San Antonio 3661).*(1./(1+delta
*(log(1./San_Antonio_3661)))));
pmax 25 caseIX re 366=(tpDSS 25 IX').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661)))));
pmax 25 caseIX ve 366=(tpDSS 25 IX').*((Vegas 3661).*(1./(1+delta*(log(
1./Vegas 3661)))));
pmax 25 caseIX gd 366=(tpDSS 25 IX').*((Goldendale 366).*(1./(1+delta*(
log(1./Goldendale 366)))));
i=1;
for i=1:8784 % operating temp 50C
    if counter caseIX 366(i) == 1
    tpDSS 50 IX(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
u50)*t(j)));
    j=j+1;
    elseif counter caseIX 366(i) == 2
    tpDSS 50 IX(i)=.83*tpDSS 50 IX(i-1);
    else
    tpDSS 50 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(6,1,1)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 50 IX(1,1:192),[0 5.278]))
% hold on
pmax 50 caseIX sa 366=(tpDSS 50 IX').*((San Antonio 3661).*(1./(1+delta
*(log(1./San Antonio 3661)))));
pmax 50 caseIX re 366=(tpDSS 50 IX').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661)))));
```

```
pmax 50 caseIX ve 366=(tpDSS 50 IX').*((Vegas 3661).*(1./(1+delta*(log(
1./Vegas 3661)))));
pmax_50_caseIX_gd_366=(tpDSS_50_IX').*((Goldendale_366).*(1./(1+delta*(
log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseIX 366(i)==1
    tpDSS 90 IX(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
u90)*t(j)));
    j=j+1;
    elseif counter caseIX 366(i)==2
    tpDSS 90 IX(i)=.83*tpDSS 90 IX(i-1);
    else
    tpDSS 90 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(6,1,2)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 90 IX(1,1:192),[0 5.278]))
% hold on
pmax 90 caseIX sa 366=(tpDSS 90 IX').*((San Antonio 3661).*(1./(1+delta
*(log(1./San Antonio 3661)))));
pmax 90 caseIX re 366=(tpDSS 90 IX').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661)))));
pmax 90 caseIX ve 366=(tpDSS 90 IX').*((Vegas_3661).*(1./(1+delta*(log(
1./Vegas 3661))));
pmax 90 caseIX qd 366=(tpDSS 90 IX').*((Goldendale 366).*(1./(1+delta*(
log(1./Goldendale 366)))));
% case-VIII: annealing twice a day
% j=1;
% for i=1:193 % operating temp 25C
      if counter caseVIII(i) == 1
00
      tpDSS 25 VIII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
9
9
      j=j+1;
8
      elseif counter caseVIII(i) == 2
00
      tpDSS 25 VIII(i)=.83*tpDSS 25 VIII(i-1);
00
      else
      tpDSS 25 VIII(i)=.946*pref/(1+gamma*(T ref-T 90));
90
      j=19; % at 11th hour the 25c degraded power is equal to the peak
90
power at 90c
8
      end
% end
% % figure
% % plot(t,mat2gray(pDSS 25,[0 5.278]),'g')
% % hold on
% % plot(t,mat2gray(tpDSS 25 VIII,[0 5.278]))
% % hold on
```

```
%
pmax 90 caseVIII1 sa=(tpDSS 25 VIII').*((San Antonio 168).*(1./(1+delta
*(log(1./San Antonio 168)))));
pmax 90 caseVIII1 re=(tpDSS 25 VIII').*((Reno 168).*(1./(1+delta*(log(1
./Reno 168)))));
pmax 90 caseVIII1 ve=(tpDSS 25 VIII').*((Vegas 168).*(1./(1+delta*(log(
1./Vegas 168)))));
pmax 90 caseVIII1 gd=(tpDSS 25 VIII').*((Goldendale 168).*(1./(1+delta*
(log(1./Goldendale 168)))));
% % figure
% % plot(t,mat2gray(pmax_90_caseVIII1_gd,[0 5.278]),'k')
% % hold on
% % plot(t,mat2gray(pmax 90 caseVIII1 sa,[0 5.278]))
% % hold on
% % plot(t,mat2gray(pmax 90 caseVIII1 re,[0 5.278]),'g')
% % hold on
% % plot(t,mat2gray(pmax 90 caseVIII1 ve,[0 5.278]),'r')
% % hold on
j=1;
for i=1:8784 % operating temp 25C
    if counter caseVIII 366(i) == 1
    tpDSS 25 VIII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j=j+1;
    elseif counter caseVIII 366(i) == 2
    tpDSS 25 VIII(i)=.83*tpDSS 25 VIII(i-1);
    else
    tpDSS 25 VIII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 11th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 VIII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseVIII1 sa 366=(tpDSS 25 VIII').*((San Antonio 3661).*(1./(1+
delta*(log(1./San Antonio 3661)))));
pmax 25 caseVIII1 re 366=(tpDSS 25 VIII').*((Reno 3661).*(1./(1+delta*(
log(1./Reno 3661)))));
pmax 25 caseVIII1 ve 366=(tpDSS 25 VIII').*((Vegas 3661).*(1./(1+delta*
(log(1./Vegas 3661))));
pmax 25 caseVIII1 gd 366=(tpDSS 25 VIII').*((Goldendale_366).*(1./(1+de
lta*(log(1./Goldendale 366))));
j=1;
for i=1:8784 % operating temp 50C
    if counter caseVIII 366(i) == 1
    tpDSS 50 VIII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-
```

```
exp((-u50)*t(j)));
```

```
j=j+1;
    elseif counter caseVIII 366(i) == 2
    tpDSS 50 VIII(i)=.83*tpDSS 50 VIII(i-1);
    else
    tpDSS 50 VIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11; % at 11th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% subplot(6,1,3)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 50 VIII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseVIII1 sa 366=(tpDSS 50 VIII').*((San Antonio 3661).*(1./(1+
delta*(log(1./San Antonio 3661))));
pmax 50 caseVIII1 re 366=(tpDSS 50 VIII').*((Reno 3661).*(1./(1+delta*(
log(1./Reno 3661))));
pmax 50 caseVIII1 ve 366=(tpDSS 50 VIII').*((Vegas 3661).*(1./(1+delta*
(log(1./Vegas 3661))));
pmax 50 caseVIII1 gd 366=(tpDSS 50 VIII').*((Goldendale 366).*(1./(1+de
lta*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseVIII 366(i) == 1
    tpDSS 90 VIII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-
exp((-u90)*t(j)));
    j=j+1;
    elseif counter caseVIII 366(i) == 2
    tpDSS 90 VIII(i)=.83*tpDSS 90 VIII(i-1);
    else
    tpDSS 90 VIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6; % at 11th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% subplot(6,1,4)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,4)
% plot(t(1,1:192),mat2gray(tpDSS 90 VIII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseVIII1 sa 366=(tpDSS 90 VIII').*((San_Antonio_3661).*(1./(1+
delta*(log(1./San Antonio 3661))));
pmax_90_caseVIII1_re_366=(tpDSS_90_VIII').*((Reno_3661).*(1./(1+delta*(
log(1./Reno 3661)))));
pmax 90 caseVIII1 ve 366=(tpDSS 90 VIII').*((Vegas 3661).*(1./(1+delta*
(log(1./Vegas 3661))));
pmax 90 caseVIII1 gd 366=(tpDSS 90 VIII').*((Goldendale 366).*(1./(1+de
lta*(log(1./Goldendale 366)))));
```

```
% case-VII: annealing thrice a day
% j=1;
% for i=1:193 % operating temp 25C
9
      if counter caseVII(i) == 1
9
      tpDSS 25 VII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
00
      j=j+1;
00
      elseif counter caseVII(i) == 2
00
     tpDSS 25 VII(i)=.83*tpDSS 25 VII(i-1);
9
      else
90
      tpDSS 25 VII(i)=.946*pref/(1+gamma*(T ref-T 90));
00
      j=19; \% at 11th hour the 25c degraded power is equal to the peak
power at 90c
00
      end
% end
% % figure
% % plot(t,mat2gray(pDSS 25,[0 5.278]),'g')
% % hold on
% % plot(t,mat2gray(tpDSS 25 VII,[0 5.278]))
% % hold on
2
pmax 90 caseVII1 sa=(tpDSS 25 VII').*((San Antonio 168).*(1./(1+delta*(
log(1./San Antonio 168)))));
0
pmax 90 caseVII1 re=(tpDSS 25 VII').*((Reno 168).*(1./(1+delta*(log(1./
Reno 168)))));
pmax 90 caseVII1 ve=(tpDSS 25 VII').*((Vegas 168).*(1./(1+delta*(log(1.
/Vegas 168)))));
00
pmax 90 caseVII1 gd=(tpDSS 25 VII').*((Goldendale 168).*(1./(1+delta*(1
oq(1./Goldendale 168))));
% % figure
% % plot(t,mat2gray(pmax 90 caseVII1 gd,[0 5.278]),'k')
% % hold on
% % plot(t,mat2gray(pmax 90 caseVII1 sa,[0 5.278]))
% % hold on
% % plot(t,mat2gray(pmax 90 caseVII1 re,[0 5.278]),'g')
% % hold on
% % plot(t,mat2gray(pmax 90 caseVII1 ve,[0 5.278]),'r')
% % hold on
j=1;
for i=1:8784 % opertating temp 25C
    if counter caseVII 366(i) == 1
    tpDSS 25 VII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j=j+1;
    elseif counter_caseVII 366(i) == 2
    tpDSS 25 VII(i)=.83*tpDSS 25 VII(i-1);
    else
    tpDSS 25 VII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is .946* peak power at
90c
    end
```

```
74
```

```
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 VII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseVII1 sa 366=(tpDSS 25 VII').*((San Antonio 3661).*(1./(1+de
lta*(log(1./San Antonio 3661)))));
pmax 25 caseVII1 re 366=(tpDSS 25 VII').*((Reno 3661).*(1./(1+delta*(lo
g(1./Reno 3661)))));
pmax 25 caseVII1 ve 366=(tpDSS 25 VII').*((Vegas 3661).*(1./(1+delta*(1
og(1./Vegas 3661)))));
pmax 25 caseVII1 gd 366=(tpDSS 25 VII').*((Goldendale 366).*(1./(1+delt
a*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % opertating temp 50C
    if counter caseVII 366(i)==1
    tpDSS 50 VII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
u50)*t(j)));
    j=j+1;
    elseif counter_caseVII_366(i) == 2
    tpDSS 50 VII(i)=.83*tpDSS 50 VII(i-1);
    else
    tpDSS 50 VII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=11; % at 10th hour the 50c degraded power is .946* peak power at
90c
    end
end
% figure
% subplot(6,1,5)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,5)
% plot(t(1,1:192),mat2gray(tpDSS 50 VII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseVII1 sa 366=(tpDSS 50 VII').*((San Antonio 3661).*(1./(1+de
lta*(log(1./San Antonio 3661))));
pmax 50 caseVII1 re 366=(tpDSS 50 VII').*((Reno 3661).*(1./(1+delta*(lo
g(1./Reno 3661))));
pmax 50 caseVII1 ve 366=(tpDSS 50 VII').*((Vegas 3661).*(1./(1+delta*(1
og(1./Vegas 3661)))));
pmax 50 caseVII1 gd 366=(tpDSS 50 VII').*((Goldendale 366).*(1./(1+delt
a*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % opertating temp 90C
    if counter caseVII 366(i) == 1
    tpDSS 90 VII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
u90)*t(j)));
    j=j+1;
    elseif counter caseVII 366(i) == 2
    tpDSS 90 VII(i)=.83*tpDSS 90 VII(i-1);
    else
```

```
tpDSS 90 VII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6; % at 10th hour the 50c degraded power is .946* peak power at
90c
    end
end
% figure
% subplot(6,1,6)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(6,1,6)
% plot(t(1,1:192),mat2gray(tpDSS 90 VII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseVII1 sa 366=(tpDSS 90 VII').*((San Antonio 3661).*(1./(1+de
lta*(log(1./San Antonio 3661)))));
pmax 90 caseVII1 re 366=(tpDSS_90_VII').*((Reno_3661).*(1./(1+delta*(lo
g(1./Reno 3661)))));
pmax 90 caseVII1 ve 366=(tpDSS 90 VII').*((Vegas 3661).*(1./(1+delta*(1
og(1./Vegas 3661)))));
pmax 90 caseVII1 qd 366=(tpDSS 90 VII').*((Goldendale 366).*(1./(1+delt
a*(log(1./Goldendale 366)))));
% case-XI 4 times annealing per day
% j=1;
% for i=1:193 % operating temp 25C
0
     if counter caseXI(i) == 1
8
      tpDSS 25 XI(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
90
      j=j+1;
90
      elseif counter caseXI(i)==2
9
      tpDSS 25 XI(i)=.83*tpDSS 25 XI(i-1);
%
      else
9
      tpDSS 25 XI(i)=.946*pref/(1+gamma*(T ref-T 90));
00
      j=19; % at 18th hour the 25c degraded power is equal to the
.946* (peak power) at 90c
9
      end
% end
% % figure
% % plot(t,tpDSS_25_XI)
% % hold on
% % plot(t,pDSS 25,'g')
%
pmax 90 caseXI sa=(tpDSS 25 XI').*((San Antonio 168).*(1./(1+delta*(log
(1./San Antonio 168)))));
2
pmax 90 caseXI re=(tpDSS 25 XI').*((Reno 168).*(1./(1+delta*(log(1./Ren
o 168)))));
pmax 90 caseXI ve=(tpDSS 25 XI').*((Vegas 168).*(1./(1+delta*(log(1./Ve
gas 168)))));
pmax 90 caseXI gd=(tpDSS 25 XI').*((Goldendale 168).*(1./(1+delta*(log(
1./Goldendale 168)))));
% % figure
% % plot(t,pmax 90 caseXI sa)
% % hold on
```

```
% % figure
% % plot(t,pmax 90 caseXI re,'g')
% % hold on
% % figure
% % plot(t,pmax 90 caseXI ve,'r')
% % hold on
% % figure
% % plot(t,pmax 90 caseXI gd,'k')
% % hold on
j=1;
for i=1:8784 % operating temp 25C
    if counter caseXI 366(i)==1
    tpDSS 25 XI(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j=j+1;
    elseif counter caseXI 366(i) == 2
    tpDSS 25 XI(i)=.83*tpDSS 25 XI(i-1);
    else
    tpDSS 25 XI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is equal to the
.946* (peak power) at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 XI(1,1:192),[0 5.278]))
% hold on
pmax_25_caseXI_sa_366=(tpDSS 25 XI').*((San Antonio 3661).*(1./(1+delta
*(log(1./San Antonio 3661)))));
pmax 25 caseXI re 366=(tpDSS 25 XI').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661)))));
pmax 25 caseXI ve 366=(tpDSS 25 XI').*((Vegas 3661).*(1./(1+delta*(log(
1./Vegas 3661)))));
pmax_25_caseXI_gd_366=(tpDSS_25 XI').*((Goldendale 366).*(1./(1+delta*(
log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 50C
    if counter caseXI 366(i) == 1
    tpDSS 50 XI(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
u50)*t(j)));
    j=j+1;
    elseif counter caseXI 366(i) == 2
    tpDSS 50 XI(i)=.83*tpDSS 50 XI(i-1);
    else
    tpDSS 50 XI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11; % at 18th hour the 25c degraded power is equal to the
.946* (peak power) at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
```

```
% plot(t(1,1:192),mat2gray(tpDSS 50 XI(1,1:192),[0 5.278]))
% hold on
pmax 50 caseXI sa 366=(tpDSS 50 XI').*((San Antonio 3661).*(1./(1+delta
*(log(1./San Antonio 3661)))));
pmax 50 caseXI re 366=(tpDSS 50 XI').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661))));
pmax 50 caseXI ve 366=(tpDSS 50 XI').*((Vegas 3661).*(1./(1+delta*(log(
1./Vegas 3661)))));
pmax 50 caseXI gd 366=(tpDSS 50 XI').*((Goldendale 366).*(1./(1+delta*(
log(1./Goldendale 366))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseXI 366(i) == 1
    tpDSS 90 XI(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
u90)*t(j)));
    j=j+1;
    elseif counter caseXI 366(i) == 2
    tpDSS 90 XI(i)=.83*tpDSS 90 XI(i-1);
    else
    tpDSS 90 XI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6; % at 18th hour the 25c degraded power is equal to the
.946* (peak power) at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 90 XI(1,1:192),[0 5.278]))
% hold on
pmax 90 caseXI sa 366=(tpDSS 90 XI').*((San Antonio 3661).*(1./(1+delta
*(log(1./San Antonio 3661))));
pmax 90 caseXI re 366=(tpDSS 90 XI').*((Reno 3661).*(1./(1+delta*(log(1
./Reno 3661))));
pmax 90 caseXI ve 366=(tpDSS 90 XI').*((Vegas 3661).*(1./(1+delta*(log(
1./Vegas 3661)))));
pmax 90 caseXI gd 366=(tpDSS 90 XI').*((Goldendale 366).*(1./(1+delta*(
log(1./Goldendale 366))));
%case-XII 5 times annealing per day
j=1;
for i=1:193 % operating temp 25C
    if counter caseXII(i) == 1
    tpDSS 25 XII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j=j+1;
    elseif counter caseXII(i) == 2
    tpDSS 25 XII(i)=.83*tpDSS 25 XII(i-1);
    else
    tpDSS 25 XII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
```

```
% plot(t,tpDSS 25 XII)
% hold on
% plot(t,pDSS 25,'g')
pmax 90 caseXII sa=(tpDSS 25 XII').*((San Antonio 168).*(1./(1+delta*(1
og(1./San Antonio 168)))));
pmax 90 caseXII re=(tpDSS 25 XII').*((Reno 168).*(1./(1+delta*(log(1./R
eno 168)))));
pmax 90 caseXII ve=(tpDSS 25 XII').*((Vegas 168).*(1./(1+delta*(log(1./
Vegas 168)))));
pmax_90_caseXII_gd=(tpDSS_25_XII').*((Goldendale_168).*(1./(1+delta*(lo
g(1./Goldendale 168)))));
% % figure
% % plot(t,pmax 90 caseXII sa,'g')
% % figure
% % plot(t,pmax 90 caseXII re,'g')
% % figure
% % plot(t,pmax 90 caseXII ve,'g')
% % figure
% % plot(t,pmax 90 caseXII gd,'g')
j=1;
for i=1:8784 % operating temp 25C
    if counter caseXII 366(i) ==1
    tpDSS 25 XII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j=j+1;
    elseif counter caseXII 366(i) == 2
    tpDSS 25 XII(i)=.83*tpDSS 25 XII(i-1);
    else
    tpDSS 25 XII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 XII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseXII sa 366=(tpDSS 25 XII').*((San Antonio 3661).*(1./(1+del
ta*(log(1./San Antonio 3661)))));
pmax 25 caseXII re 366=(tpDSS 25 XII').*((Reno 3661).*(1./(1+delta*(log
(1./Reno 3661))));
pmax 25 caseXII ve 366=(tpDSS 25 XII').*((Vegas 3661).*(1./(1+delta*(lo
g(1./Vegas 3661)))));
pmax 25 caseXII gd 366=(tpDSS 25 XII').*((Goldendale 366).*(1./(1+delta
*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 50C
    if counter caseXII 366(i) == 1
    tpDSS 50 XII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
u50)*t(j)));
    j=j+1;
    elseif counter caseXII 366(i) == 2
```

```
tpDSS 50 XII(i)=.83*tpDSS 50 XII(i-1);
    else
    tpDSS 50 XII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=11; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 50 XII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseXII sa 366=(tpDSS 50 XII').*((San Antonio 3661).*(1./(1+del
ta*(log(1./San Antonio 3661)))));
pmax 50 caseXII re 366=(tpDSS 50 XII').*((Reno 3661).*(1./(1+delta*(log
(1./Reno 3661))));
pmax 50 caseXII ve 366=(tpDSS 50 XII').*((Vegas 3661).*(1./(1+delta*(lo
g(1./Vegas 3661)))));
pmax 50 caseXII qd 366=(tpDSS 50 XII').*((Goldendale 366).*(1./(1+delta
*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseXII 366(i) == 1
    tpDSS 90 XII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
u90)*t(j)));
    j=j+1;
    elseif counter caseXII 366(i)==2
    tpDSS 90 XII(i)=.83*tpDSS 90 XII(i-1);
    else
    tpDSS 90 XII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 90 XII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseXII sa 366=(tpDSS 90 XII').*((San Antonio 3661).*(1./(1+del
ta*(log(1./San Antonio 3661)))));
pmax 90 caseXII re 366=(tpDSS 90 XII').*((Reno 3661).*(1./(1+delta*(log
(1./Reno 3661))));
pmax 90 caseXII ve 366=(tpDSS 90 XII').*((Vegas 3661).*(1./(1+delta*(lo
g(1./Vegas 3661)))));
pmax 90 caseXII gd 366=(tpDSS 90 XII').*((Goldendale 366).*(1./(1+delta
*(log(1./Goldendale 366)))));
%case-XIII 6 times annealing per day
j=1;
for i=1:193 % operating temp 25C
    if counter caseXIII(i) == 1
    tpDSS 25 XIII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
```

```
j=j+1;
    elseif counter caseXIII(i) == 2
    tpDSS 25 XIII(i)=.83*tpDSS 25 XIII(i-1);
    else
    tpDSS 25 XIII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t,tpDSS 25 XIII)
% hold on
% plot(t,pDSS 25,'g')
pmax_90_caseXIII_sa=(tpDSS_25_XIII').*((San_Antonio_168).*(1./(1+delta*
(log(1./San Antonio 168))));
pmax 90 caseXIII re=(tpDSS 25 XIII').*((Reno 168).*(1./(1+delta*(log(1.
/Reno 168)))));
pmax 90 caseXIII ve=(tpDSS 25 XIII').*((Vegas 168).*(1./(1+delta*(log(1
./Vegas 168)))));
pmax 90 caseXIII gd=(tpDSS 25 XIII').*((Goldendale 168).*(1./(1+delta*(
log(1./Goldendale 168)))));
% % figure
% % plot(t,pmax 90 caseXIII sa,'g')
% % figure
% % plot(t,pmax 90 caseXIII re,'g')
% % figure
% % plot(t,pmax 90 caseXIII ve,'g')
% % figure
% % plot(t,pmax 90 caseXIII gd,'g')
j=1;
for i=1:8784 % operating temp 25C
    if counter caseXIII 366(i) == 1
    tpDSS 25 XIII(i)=pref-(kdss25*pref)*(1-exp((-u25)*t(j)));
    j = j + 1;
    elseif counter caseXIII 366(i) == 2
    tpDSS 25 XIII(i)=.83*tpDSS_25_XIII(i-1);
    else
    tpDSS 25 XIII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 25 XIII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseXIII sa 366=(tpDSS 25 XIII').*((San Antonio 3661).*(1./(1+d
elta*(log(1./San Antonio 3661))));
pmax 25 caseXIII re 366=(tpDSS 25 XIII').*((Reno 3661).*(1./(1+delta*(1
og(1./Reno 3661))));
pmax 25 caseXIII ve 366=(tpDSS 25 XIII').*((Vegas 3661).*(1./(1+delta*(
log(1./Vegas 3661))));
```

```
pmax 25 caseXIII gd 366=(tpDSS 25 XIII').*((Goldendale 366).*(1./(1+del
ta*(log(1./Goldendale 366))));
j=1;
for i=1:8784 % operating temp 50C
    if counter caseXIII 366(i) == 1
    tpDSS 50 XIII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-
exp((-u50)*t(j)));
    j=j+1;
    elseif counter caseXIII 366(i)==2
    tpDSS 50 XIII(i)=.83*tpDSS 50 XIII(i-1);
    else
    tpDSS 50 XIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 50 XIII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseXIII sa 366=(tpDSS 50 XIII').*((San Antonio 3661).*(1./(1+d
elta*(log(1./San Antonio 3661)))));
pmax 50 caseXIII re 366=(tpDSS 50 XIII').*((Reno 3661).*(1./(1+delta*(1
og(1./Reno 3661))));
pmax 50 caseXIII ve 366=(tpDSS 50 XIII').*((Vegas 3661).*(1./(1+delta*(
log(1./Vegas 3661)))));
pmax 50 caseXIII gd 366=(tpDSS 50 XIII').*((Goldendale 366).*(1./(1+del
ta*(log(1./Goldendale 366)))));
j=1;
for i=1:8784 % operating temp 90C
    if counter caseXIII 366(i) ==1
    tpDSS 90 XIII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-
exp((-u90)*t(j)));
    j=j+1;
    elseif counter caseXIII 366(i)==2
    tpDSS 90 XIII(i)=.83*tpDSS 90 XIII(i-1);
    else
    tpDSS 90 XIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6; % at 18th hour the 25c degraded power is equal to the peak
power at 90c
    end
end
% figure
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:192),mat2gray(tpDSS 90 XIII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseXIII sa 366=(tpDSS 90 XIII').*((San Antonio 3661).*(1./(1+d
elta*(log(1./San Antonio 3661))));
pmax 90 caseXIII re 366=(tpDSS 90 XIII').*((Reno 3661).*(1./(1+delta*(1
og(1./Reno 3661)))));
```

```
pmax 90 caseXIII ve 366=(tpDSS 90 XIII').*((Vegas 3661).*(1./(1+delta*(
log(1./Vegas 3661))));
pmax 90 caseXIII gd 366=(tpDSS 90 XIII').*((Goldendale 366).*(1./(1+del
ta*(log(1./Goldendale 366)))));
% analysis
% plot(t,pmax 25 caseV sa)
% hold on
% plot(t,pmax 90 caseVII1 sa,'g')
% hold on
% plot(t,pmax_90_caseVIII1 sa,'r')
% hold on
% plot(t,pmax 90 caseIX sa,'g')
% hold on
% plot(t,pmax 90 caseX sa,'r')
%
area 1sun=[trapz(pDSS 90),trapz(tpDSS 90 X),trapz(tpDSS 90 IX),trapz(tp
DSS 25 VIII), trapz(tpDSS 25 VII), trapz(tpDSS 25 XI), trapz(tpDSS 25 XII)
,trapz(tpDSS 25 XIII)]
2
area sa=[trapz(pmax 90 caseVI sa),trapz(pmax 90 caseX sa),trapz(pmax 90
_caseIX_sa),trapz(pmax_90_caseVIII1_sa),trapz(pmax_90_caseVII1_sa),trap
z(pmax 90 caseXI sa),trapz(pmax_90_caseXII_sa),trapz(pmax_90_caseXIII_s
a)]
0
area re=[trapz(pmax 90 caseVI re),trapz(pmax 90 caseX re),trapz(pmax 90
caseIX re), trapz (pmax 90 caseVIII1 re), trapz (pmax 90 caseVII1 re), trap
z(pmax 90 caseXI re),trapz(pmax 90 caseXII re),trapz(pmax 90 caseXIII r
e)]
90
area ve=[trapz(pmax 90 caseVI ve),trapz(pmax 90 caseX ve),trapz(pmax 90
caseIX ve), trapz (pmax 90 caseVIII1 ve), trapz (pmax 90 caseVII1 ve), trap
z(pmax 90 caseXI ve),trapz(pmax 90 caseXII ve),trapz(pmax 90 caseXIII v
e)]
8
area gd=[trapz(pmax 90 caseVI gd),trapz(pmax 90 caseX gd),trapz(pmax 90
caseIX gd),trapz(pmax 90 caseVIII1 gd),trapz(pmax 90 caseVII1 gd),trap
z(pmax 90 caseXI gd),trapz(pmax 90 caseXII gd),trapz(pmax 90 caseXIII g
d)]
d=[0,0.5,1,2,3,4,5,6]; % no of annealing per day
% figure
% plot(d, area 1sun)
% hold on
% figure
% plot(d, area gd, 'k')
% hold on
% plot(d,area_sa)
% hold on
% plot(d,area re,'g')
% hold on
% plot(d,area ve,'r')
% hold on
```

```
area 1sun 366=[trapz(pDSS 90),trapz(tpDSS 90 X),trapz(tpDSS 90 IX),trap
z(tpDSS 25 VIII),trapz(tpDSS 25 VII),trapz(tpDSS 25 XI),trapz(tpDSS 25
XII),trapz(tpDSS_25_XIII)];
area sa 366=[trapz(pmax 90 caseVI sa 366),trapz(pmax 90 caseX sa 366),t
rapz(pmax 90 caseIX sa 366),trapz(pmax 90 caseVIII1 sa 366),trapz(pmax
90 caseVII1 sa 366), trapz(pmax 90 caseXI sa 366), trapz(pmax 90 caseXII
sa 366),trapz(pmax 90 caseXIII sa 366)];
area re 366=[trapz(pmax 90 caseVI re 366),trapz(pmax 90 caseX re 366),t
rapz(pmax 90 caseIX re 366),trapz(pmax 90 caseVIII1 re 366),trapz(pmax
90_caseVII1_re_366),trapz(pmax_90_caseXI_re_366),trapz(pmax_90_caseXII_
re_366),trapz(pmax_90_caseXIII_re_366)];
area ve 366=[trapz(pmax 90 caseVI ve 366),trapz(pmax 90 caseX ve 366),t
rapz(pmax 90 caseIX ve 366),trapz(pmax 90 caseVIII1 ve 366),trapz(pmax
90_caseVII1_ve_366),trapz(pmax_90_caseXI_ve_366),trapz(pmax_90_caseXII
ve 366), trapz(pmax 90 caseXIII ve 366)];
area gd 366=[trapz(pmax 90 caseVI gd 366),trapz(pmax 90 caseX gd 366),t
rapz(pmax 90 caseIX gd 366),trapz(pmax 90 caseVIII1 gd 366),trapz(pmax
90 caseVII1 gd 366), trapz(pmax 90 caseXI gd 366), trapz(pmax 90 caseXII
gd 366),trapz(pmax 90 caseXIII gd 366)];
figure
% plot(d,area 1sun 366)
% hold on
% figure
% plot(d,area gd 366,'k')
% hold on
% plot(d, area sa 366)
% hold on
% plot(d,area re 366,'g')
% hold on
% plot(d,area ve 366,'r')
% hold on
area 1sun 366 25=[trapz(pDSS 25),trapz(tpDSS 25 X),trapz(tpDSS 25 IX),t
rapz(tpDSS 25 VIII),trapz(tpDSS 25 VII),trapz(tpDSS 25 XI),trapz(tpDSS
25 XII), trapz(tpDSS 25 XIII)]
area sa 366 25=[trapz(pmax 25 caseV sa 366),trapz(pmax 25 caseX sa 366)
,trapz(pmax 25 caseIX sa 366),trapz(pmax 25 caseVIII1 sa 366),trapz(pma
x 25 caseVII1 sa 366),trapz(pmax 25 caseXI sa 366),trapz(pmax 25 caseXI
I_sa_366),trapz(pmax_25_caseXIII_sa_366)]
area_re_366_25=[trapz(pmax_25_caseV_re_366),trapz(pmax_25_caseX_re_366)
,trapz(pmax_25_caseIX_re_366),trapz(pmax_25_caseVIII1_re_366),trapz(pma
x_25_caseVII1_re_366),trapz(pmax_25_caseXI_re_366),trapz(pmax_25_caseXI
I re 366), trapz(pmax 25 caseXIII re 366)]
area ve 366 25=[trapz(pmax 25 caseV ve 366),trapz(pmax 25 caseX ve 366)
,trapz(pmax 25 caseIX ve 366),trapz(pmax 25 caseVIII1 ve 366),trapz(pma
x 25 caseVII1 ve 366), trapz(pmax 25 caseXI ve 366), trapz(pmax 25 caseXI
I ve 366), trapz (pmax 25 caseXIII ve 366)]
area gd 366 25=[trapz(pmax 25 caseV gd 366),trapz(pmax 25 caseX gd 366)
,trapz(pmax_25_caseIX_gd_366),trapz(pmax_25_caseVIII1_gd_366),trapz(pma
x 25 caseVII1 gd 366),trapz(pmax 25 caseXI gd 366),trapz(pmax 25 caseXI
I gd 366), trapz(pmax 25 caseXIII gd 366)]
area 1sun 366 25=area 1sun 366 25/1000000;
area sa 366 25=area sa 366 25/1000000;
area re 366 25=area re 366 25/1000000;
```

```
84
```

```
area ve 366 25=area ve 366 25/1000000;
area gd 366 25=area gd 366 25/1000000;
% figure
% plot(d, area 1sun 366 25)
% hold on
% figure
% subplot(3,1,1)
% plot(d,area gd 366 25,'k')
% hold on
% subplot(3,1,1)
% plot(d,area sa 366 25)
% hold on
% subplot(3,1,1)
% plot(d,area_re_366_25,'g')
% hold on
% subplot(3,1,1)
% plot(d,area ve 366 25,'r')
% hold on
50_XII), trapz(tpDSS_50_XIII)]
```

```
area 1sun 366 50=[trapz(pDSS 50),trapz(tpDSS 50 X),trapz(tpDSS 50 IX),t
rapz(tpDSS 50 VIII),trapz(tpDSS 50 VII),trapz(tpDSS 50 XI),trapz(tpDSS
area sa 366 50=[trapz(pmax 50 caseV sa 366),trapz(pmax 50 caseX sa 366)
,trapz(pmax 50 caseIX sa 366),trapz(pmax 50 caseVIII1 sa 366),trapz(pma
x 50 caseVII1 sa 366), trapz(pmax 50 caseXI sa 366), trapz(pmax 50 caseXI
I sa 366), trapz(pmax 50 caseXIII sa 366)]
area re 366 50=[trapz(pmax 50 caseV re 366),trapz(pmax 50 caseX re 366)
,trapz(pmax 50 caseIX re 366),trapz(pmax 50 caseVIII1 re 366),trapz(pma
x 50 caseVII1 re 366),trapz(pmax 50 caseXI re 366),trapz(pmax 50 caseXI
I re 366), trapz(pmax 50 caseXIII re 366)]
area ve 366 50=[trapz(pmax 50 caseV ve 366),trapz(pmax 50 caseX ve 366)
,trapz(pmax 50 caseIX ve 366),trapz(pmax 50 caseVIII1 ve 366),trapz(pma
x 50 caseVII1 ve 366), trapz(pmax 50 caseXI ve 366), trapz(pmax 50 caseXI
I ve 366), trapz(pmax 50 caseXIII ve 366)]
area gd 366 50=[trapz(pmax 50 caseV gd 366),trapz(pmax 50 caseX gd 366)
,trapz(pmax 50 caseIX gd 366),trapz(pmax 50 caseVIII1 gd 366),trapz(pma
x 50 caseVII1 gd 366),trapz(pmax 50 caseXI gd 366),trapz(pmax 50 caseXI
I gd 366), trapz(pmax 50 caseXIII gd 366)]
area 1sun 366 50=area 1sun 366 50/1000000;
area sa 366 50=area sa 366 50/1000000;
area re 366 50=area re 366 50/1000000;
area_ve_366_50=area_ve_366_50/1000000;
area gd 366 50=area gd 366 50/1000000;
% figure
% plot(d,area 1sun 366 50,'k')
% hold on
% figure
% subplot(3,1,2)
% plot(d,area gd 366 50,'k')
% hold on
% subplot(3,1,2)
% plot(d, area sa 366 50)
% hold on
```

```
% subplot(3,1,2)
```
```
% plot(d,area_re_366_50,'g')
% hold on
% subplot(3,1,2)
% plot(d,area_ve_366_50,'r')
% hold on
```

% ylim(ax(1),[0 0.6]); % ylim(ax(2),[0 0.7]);

```
area 1sun 366 90=[trapz(pDSS 90),trapz(tpDSS 90 X),trapz(tpDSS 90 IX),t
rapz(tpDSS 90 VIII),trapz(tpDSS 90 VII),trapz(tpDSS 90 XI),trapz(tpDSS
90 XII), trapz(tpDSS 90 XIII)]
area sa 366 90=[trapz(pmax 90 caseVI sa 366),trapz(pmax 90 caseX sa 366
),trapz(pmax 90 caseIX sa 366),trapz(pmax 90 caseVIII1 sa 366),trapz(pm
ax_90_caseVII1_sa_366),trapz(pmax 90 caseXI sa 366),trapz(pmax 90 caseX
II_sa_366),trapz(pmax_90_caseXIII sa 366)]
area re 366 90=[trapz(pmax 90 caseVI re 366),trapz(pmax 90 caseX re 366
),trapz(pmax 90 caseIX re 366),trapz(pmax 90 caseVIII1 re 366),trapz(pm
ax 90 caseVII1 re 366), trapz(pmax 90 caseXI re 366), trapz(pmax 90 caseX
II re 366),trapz(pmax 90 caseXIII re 366)]
area ve 366 90=[trapz(pmax 90 caseVI ve 366),trapz(pmax 90 caseX ve 366
),trapz(pmax 90 caseIX ve 366),trapz(pmax 90 caseVIII1 ve 366),trapz(pm
ax 90 caseVII1 ve 366), trapz(pmax 90 caseXI ve 366), trapz(pmax 90 caseX
II_ve_366),trapz(pmax_90_caseXIII_ve_366)]
area_gd_366_90=[trapz(pmax_90_caseVI_gd_366),trapz(pmax_90_caseX_gd_366
), trapz(pmax 90 caseIX gd 366), trapz(pmax 90 caseVIII1 gd 366), trapz(pm
ax 90 caseVII1 gd 366), trapz(pmax 90 caseXI gd 366), trapz(pmax 90 caseX
II gd 366),trapz(pmax 90 caseXIII gd 366)]
area Isun 366 90=area Isun 366 90/1000000;
area_sa_366_90=area_sa_366_90/1000000;
area_re_366_90=area_re_366_90/1000000;
area ve 366 90=area ve 366 90/1000000;
area gd 366 90=area gd 366 90/1000000;
% figure
% plot(d, area 1sun 366 90)
% hold on
% figure
% subplot(3,1,3)
% plot(d,area gd 366 90,'k')
% hold on
% subplot(3,1,3)
% plot(d,area sa 366 90)
% hold on
% subplot(3,1,3)
% plot(d,area re 366 90,'g')
% hold on
% subplot(3,1,3)
% plot(d,area ve 366 90,'r')
% hold on
% figure
% [ax,h1,h2]=plotyy(t(1,1:25),mat2gray(pmax 90 caseVI sa(25:49,1),[0
5.278]),t(1,1:25),San Antonio 168(25:49,1));
% hold on
```

```
% set(get(ax(1),'Ylabel'),'String','Normalized Max Power (a.u.)');
% set(get(ax(2),'Ylabel'),'String','Solar Irradiance(kW/m^2)');
% set(ax(1),'fontsize',18,'fontweight','d','YColor',[0 0
0], 'fontname', 'times new roman');
% set(ax(2),'fontsize',18,'fontweight','d','YColor',[0 0
0], 'fontname', 'times new roman');
% plot(t(1,1:25),mat2gray(pmax 90 caseX sa(25:49,1),[0 5.278]),'r')
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseIX sa(25:49,1),[0 5.278]),'g')
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseVIII1 sa(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseVII1 sa(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXI sa(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXII sa(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXIII sa(25:49,1),[0 5.278]))
% hold on
% figure
2
[ax,h1,h2]=plotyy(t(1,1:25),mat2gray(pmax 90 caseVI sa 366(25:49,1),[0
5.278]),t(1,1:25),San Antonio 3661(25:49,1));
% hold on
% ylim(ax(1),[0 0.6]);
% ylim(ax(2),[0 0.7]);
% set(get(ax(1),'Ylabel'),'String','Normalized Max Power (mW)');
% set(get(ax(2),'Ylabel'),'String','Solar Irradiance(kW/m^2)');
% set(ax(1),'fontsize',18,'fontweight','d','YColor',[0 0
0], 'fontname', 'times new roman');
% set(ax(2),'fontsize',18,'fontweight','d','YColor',[0 0
0], 'fontname', 'times new roman');
% plot(t(1,1:25),mat2gray(pmax 90 caseX sa 366(25:49,1),[0 5.278]),'r')
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseIX sa 366(25:49,1),[0
5.278]), 'q')
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseVIII1 sa 366(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseVII1 sa 366(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXI sa 366(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXII sa 366(25:49,1),[0 5.278]))
% hold on
% plot(t(1,1:25),mat2gray(pmax 90 caseXIII sa 366(25:49,1),[0 5.278]))
% hold on
% figure
% plot(t(1,1:61),mat2gray(pDSS 90(1:61,1),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 X(1,1:61),[0 5.278]))
```

```
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 IX(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 25 VIII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 25 VII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 25 XI(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS_25_XII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 25 XIII(1,1:61),[0 5.278]))
% hold on
% figure
% plot(t(1,1:61),mat2gray(pDSS 90(1:61,1),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 X(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 IX(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 VIII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 VII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 XI(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 XII(1,1:61),[0 5.278]))
% hold on
% plot(t(1,1:61),mat2gray(tpDSS 90 XIII(1,1:61),[0 5.278]))
% hold on
```

Appendix II

Program Code: Outdoor Temperature Simulation

```
clc
clear all
close all
load counter caseIII new.csv
load counter caseIV new.csv
load counter caseV new.csv
load counter caseVI new.csv
load counter_caseVII_new.csv
load counter caseVIII new.csv
load counter caseIX new.csv
load ANCHORAGE INTL ARPT AL1.csv
load APALACHICOLA MUNI FL1.csv
load ASPEN PITKIN COl.csv
load CASA GRANDE MUNI AZ1.csv
% load loc storage.xlsx
% load radwx 110753545 1998.csv
prompt={'Enter USAF ID:', 'Year:', 'Region:'};
loc=inputdlg(prompt, 'Location and Year')
if loc{3,1} == 'NA'
    pos=1;
end
if loc{3,1}=='CA'
    pos=2;
end
if loc{3,1}=='EU'
   pos=3;
end
% North America
if (pos==1)
    U = strcat(loc{1,1}, ' ', loc{2,1}, ' solar.csv');
    act dat=importdata(U);
    act dat1(1:8760,1)=act dat.data(1:length(act dat.data),14)/1000;
end
% Western Canada
% if (-130<str2num(loc{1,1}) && str2num(loc{1,1})<-89) &&
(49<str2num(loc{2,1}) && str2num(loc{2,1})<58) && (pos==2)
      U = strcat('site_',loc{2,1},'_',loc{1,1},'_timeseries.csv');
8
00
      act dat=load(U);
      act dat1(1:8760,1)=act dat(8:8767,6)/10000;
8
% end
```

```
delta=0.063;
gamma=-0.002;
t=[0:8759];
pref=5.2825;
T 25=273+25;
T<sup>50=273+50</sup>;
T 90=273+90;
T ref=273+25;
udss25=0.03601;
udss50=0.07552;
udss90=0.2097;
kdss25=0.3450;
kdss50=0.2154;
kdss90=0.07917;
quant1=1000;
quant2=1600;
T inc1=(T 50-T 25)/quant1;
T inc2=(T 90-T 50)/quant2;
kdss incl=(kdss50-kdss25)/quant1;
kdss inc2=(kdss90-kdss50)/quant2;
udss_inc1=(udss50-udss25)/quant1;
udss inc2=(udss90-udss50)/quant2;
for (i=1:2601)
    if i<1001
        T(i)=T 25+((i-1)*T inc1);
        k(i)=kdss25+((i-1)*kdss inc1);
        u(i)=udss25+((i-1)*udss inc1);
    else
        T(i) = T 50 + ((i-1001) * T inc2);
        k(i)=kdss50+((i-1001)*kdss inc2);
        u(i)=udss50+((i-1001)*udss inc2);
    end
end
a1=146.7;
b1=-0.0202;
k fit=a1*exp(b1*T);
a2=2.147e-005;
b2=0.0255;
u fit=a2*exp(b2*T);
figure
plot(T,k)
hold on
plot(T,k fit,'k')
hold on
figure
plot(T,u)
hold on
plot(T,u fit,'k')
hold on
% case-I: under 1 sun without annealing
pmax 50=pref/(1+gamma*(T ref-T 50));
pmax 90=pref/(1+gamma*(T ref-T 90));
```

```
90
```

```
tpDSS 90=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t));
tpDSS 50=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t));
tpDSS 25=pref-(kdss25*pref)*(1-exp((-udss25)*t));
pDSS 90=tpDSS 90.';
pDSS 50=tpDSS 50.';
pDSS 25=tpDSS 25.';
% figure
% plot(t,mat2gray(pDSS 25,[0 5.278]),'g')
% hold on
% plot(t,mat2gray(pDSS 50,[0 5.278]))
% hold on
% plot(t,mat2gray(pDSS 90,[0 5.278]),'r')
\ case-II: under normal sun without aneealing
pmax 25 caseII=(pDSS 25).*((act dat1(1:8760,1)).*(1./(1+delta*(log(1./a
ct dat1(1:8760,1)))));
pmax 50 caseII=(pDSS 50).*((act dat1(1:8760,1)).*(1./(1+delta*(log(1./a
ct dat1(1:8760,1)))));
pmax 90 caseII=(pDSS 90).*((act dat1(1:8760,1)).*(1./(1+delta*(log(1./a
ct dat1(1:8760,1)))));
% case-III: annealing once per 2 days
j=1;
for i=1:8760 % operating temp 25C
    if counter caseIII new(i) == 1
    tpDSS 25 III(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseIII new(i)==2
    tpDSS 25 III(i)=.83*tpDSS 25 III(i-1);
    else
    tpDSS 25 III(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax_25_caseIII=(tpDSS_25_III').*((act_dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseIII new(i)==1
    tpDSS 50 III(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
```

```
j=j+1;
    elseif counter caseIII new(i) == 2
    tpDSS_50_III(i)=.83*tpDSS 50 III(i-1);
    else
    tpDSS 50 III(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS_50_III(1,1:192),[0 5.278]))
% hold on
pmax 50 caseIII=(tpDSS 50 III').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseIII new(i) == 1
    tpDSS 90 III(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter caseIII new(i) == 2
    tpDSS 90 III(i)=.83*tpDSS 90 III(i-1);
    else
    tpDSS 90 III(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 III(1,1:192),[0 5.278]))
% hold on
pmax 90 caseIII=(tpDSS 90 III').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
% case-IV: annealing once per day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseIV new(i) ==1
    tpDSS 25 IV(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseIV new(i) == 2
    tpDSS 25 IV(i)=.83*tpDSS 25 IV(i-1);
    else
    tpDSS 25 IV(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
```

```
end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 IV(1,1:192),[0 5.278]))
% hold on
pmax 25 caseIV=(tpDSS 25 IV').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseIV new(i)==1
    tpDSS 50 IV(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
    j=j+1;
    elseif counter caseIV new(i)==2
    tpDSS 50 IV(i)=.83*tpDSS 50 IV(i-1);
    else
    tpDSS 50 IV(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 IV(1,1:192),[0 5.278]))
% hold on
pmax 50 caseIV=(tpDSS 50 IV').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseIV new(i) == 1
    tpDSS 90 IV(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter caseIV new(i) == 2
    tpDSS 90 IV(i)=.83*tpDSS 90 IV(i-1);
    else
    tpDSS 90 IV(i)=.946*pref/(1+gamma*(T_ref-T_90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 IV(1,1:192),[0 5.278]))
```

```
% hold on
pmax 90 caseIV=(tpDSS 90 IV').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
% case-V: annealing twice a day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseV new(i) == 1
    tpDSS 25 V(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseV new(i) == 2
    tpDSS 25 V(i)=.83*tpDSS 25 V(i-1);
    else
    tpDSS 25 V(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 V(1,1:192),[0 5.278]))
% hold on
pmax 25 caseV=(tpDSS 25 V').*((act dat1(1:8760,1)).*(1./(1+delta*(log(1
./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseV new(i) ==1
    tpDSS 50 V(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
    j=j+1;
    elseif counter caseV new(i) == 2
    tpDSS 50 V(i)=.83*tpDSS 50 V(i-1);
    else
    tpDSS 50 V(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 V(1,1:192),[0 5.278]))
% hold on
pmax 50 caseV=(tpDSS 50 V').*((act dat1(1:8760,1)).*(1./(1+delta*(log(1
./act dat1(1:8760,1)))));
i=1;
for i=1:8760 % operating temp 90C
```

```
if counter caseV new(i) ==1
    tpDSS 90 V(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter caseV new(i) == 2
    tpDSS 90 V(i)=.83*tpDSS 90 V(i-1);
    else
    tpDSS 90 V(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS_90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 V(1,1:192),[0 5.278]))
% hold on
pmax 90 caseV=(tpDSS 90 V').*((act dat1(1:8760,1)).*(1./(1+delta*(log(1
./act dat1(1:8760,1)))));
% case-VI: annealing thrice a day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseVI new(i) == 1
    tpDSS 25 VI(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseVI new(i) == 2
    tpDSS 25 VI(i)=.83*tpDSS 25 VI(i-1);
    else
    tpDSS 25 VI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 VI(1,1:192),[0 5.278]))
% hold on
pmax 25 caseVI=(tpDSS 25 VI').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseVI new(i) == 1
    tpDSS 50 VI(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
    j=j+1;
    elseif counter caseVI new(i) == 2
    tpDSS 50 VI(i)=.83*tpDSS 50 VI(i-1);
```

```
else
    tpDSS 50 VI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 VI(1,1:192),[0 5.278]))
% hold on
pmax 50 caseVI=(tpDSS 50 VI').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseVI new(i) == 1
    tpDSS 90 VI(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter_caseVI_new(i) == 2
    tpDSS 90 VI(i)=.83*tpDSS 90 VI(i-1);
    else
    tpDSS 90 VI(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 VI(1,1:192),[0 5.278]))
% hold on
pmax 90 caseVI=(tpDSS 90 VI').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
% case-VII: annealing four times a day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseVII new(i) == 1
    tpDSS 25 VII(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseVII new(i) == 2
    tpDSS 25 VII(i)=.83*tpDSS 25 VII(i-1);
    else
    tpDSS 25 VII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
```

```
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 VII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseVII=(tpDSS 25 VII').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseVII new(i) == 1
    tpDSS 50 VII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
    j=j+1;
    elseif counter caseVII new(i) == 2
    tpDSS 50 VII(i)=.83*tpDSS 50 VII(i-1);
    else
    tpDSS 50 VII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 VII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseVII=(tpDSS 50 VII').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseVII new(i) ==1
    tpDSS 90 VII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter caseVII new(i) == 2
    tpDSS_90_VII(i)=.83*tpDSS 90 VII(i-1);
    else
    tpDSS 90 VII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 VII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseVII=(tpDSS 90 VII').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
```

```
% case-VIII: annealing five times a day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseVIII new(i)==1
    tpDSS 25 VIII(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-
exp((-udss25)*t(j)));
    j=j+1;
    elseif counter caseVIII new(i) == 2
    tpDSS 25 VIII(i)=.83*tpDSS 25 VIII(i-1);
    else
    tpDSS 25 VIII(i) = .946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 VIII(1,1:192),[0 5.278]))
% hold on
pmax 25 caseVIII=(tpDSS 25 VIII').*((act dat1(1:8760,1)).*(1./(1+delta*
(log(1./act dat1(1:8760,1)))));
i=1;
for i=1:8760 % operating temp 50C
    if counter caseVIII new(i) == 1
    tpDSS 50 VIII(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-
exp((-udss50)*t(j)));
    j=j+1;
    elseif counter caseVIII new(i)==2
    tpDSS 50 VIII(i)=.83*tpDSS 50 VIII(i-1);
    else
    tpDSS 50 VIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
    end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 VIII(1,1:192),[0 5.278]))
% hold on
pmax 50 caseVIII=(tpDSS 50 VIII').*((act dat1(1:8760,1)).*(1./(1+delta*
(log(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseVIII new(i) == 1
    tpDSS 90 VIII(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-
exp((-udss90)*t(j)));
```

```
j=j+1;
    elseif counter caseVIII new(i) == 2
    tpDSS 90 VIII(i)=.83*tpDSS 90 VIII(i-1);
    else
    tpDSS 90 VIII(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS_90_VIII(1,1:192),[0 5.278]))
% hold on
pmax 90 caseVIII=(tpDSS 90 VIII').*((act dat1(1:8760,1)).*(1./(1+delta*
(log(1./act dat1(1:8760,1)))));
% case-IX: annealing six times a day
j=1;
for i=1:8760 % operating temp 25C
    if counter caseIX new(i)==1
    tpDSS 25 IX(i)=pref/(1+gamma*(T ref-T 25))-(kdss25*pref)*(1-exp((-
udss25)*t(j)));
    j=j+1;
    elseif counter caseIX new(i) == 2
    tpDSS 25 IX(i)=.83*tpDSS 25 IX(i-1);
    else
    tpDSS 25 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=19;
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 IX(1,1:192),[0 5.278]))
% hold on
pmax 25 caseIX=(tpDSS 25 IX').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 50C
    if counter caseIX new(i)==1
    tpDSS 50 IX(i)=pref/(1+gamma*(T ref-T 50))-(kdss50*pref)*(1-exp((-
udss50)*t(j)));
    j=j+1;
    elseif counter caseIX new(i) == 2
    tpDSS 50 IX(i)=.83*tpDSS 50 IX(i-1);
    else
    tpDSS 50 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=11;
```

```
end
end
% figure
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(pDSS 50(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,2)
% plot(t(1,1:192),mat2gray(tpDSS 50 IX(1,1:192),[0 5.278]))
% hold on
pmax_50_caseIX=(tpDSS_50_IX').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
j=1;
for i=1:8760 % operating temp 90C
    if counter caseIX new(i) == 1
    tpDSS 90 IX(i)=pref/(1+gamma*(T ref-T 90))-(kdss90*pref)*(1-exp((-
udss90)*t(j)));
    j=j+1;
    elseif counter caseIX new(i) == 2
    tpDSS_90_IX(i) = .83*tpDSS 90 IX(i-1);
    else
    tpDSS 90 IX(i)=.946*pref/(1+gamma*(T ref-T 90));
    j=6;
    end
end
% figure
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(pDSS 90(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,3)
% plot(t(1,1:192),mat2gray(tpDSS 90 IX(1,1:192),[0 5.278]))
% hold on
pmax 90 caseIX=(tpDSS 90 IX').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
% analysis
d=[0,0.5,1,2,3,4,5,6]; % no of annealing per day
area 1sun 25=[trapz(pDSS 25),trapz(tpDSS 25 III),trapz(tpDSS 25 IV),tra
pz(tpDSS 25 V),trapz(tpDSS 25 VI),trapz(tpDSS 25 VII),trapz(tpDSS 25 VI
II),trapz(tpDSS 25 IX)];
area loc 25=[trapz(pmax 25 caseII),trapz(pmax 25 caseIII),trapz(pmax 25
caseIV), trapz (pmax 25 caseV), trapz (pmax 25 caseVI), trapz (pmax 25 caseV
II), trapz(pmax 25 caseVIII), trapz(pmax 25 caseIX)];
area 1sun 25=area 1sun 25/1000000;
area_loc_25=area_loc_25/1000000;
% figure
% plot(d, area 1sun 25)
% hold on
figure
% subplot(3,1,1)
plot(d, area loc 25, 'k')
hold on
```

```
area 1sun 50=[trapz(pDSS 50),trapz(tpDSS 50 III),trapz(tpDSS 50 IV),tra
pz(tpDSS 50 V),trapz(tpDSS 50 VI),trapz(tpDSS 50 VII),trapz(tpDSS 50 VI
II),trapz(tpDSS 50 IX)];
area loc 50=[trapz(pmax 50 caseII),trapz(pmax 50 caseIII),trapz(pmax 50
caseIV), trapz (pmax 50 caseV), trapz (pmax 50 caseVI), trapz (pmax 50 caseV
II),trapz(pmax 50 caseVIII),trapz(pmax 50 caseIX)];
area_1sun_50=area_1sun_50/1000000;
area loc 50=area loc 50/1000000;
% figure
% plot(d,area 1sun 50)
% hold on
% figure
% subplot(3,1,1)
plot(d, area loc 50, 'g')
hold on
area 1sun 90=[trapz(pDSS 90),trapz(tpDSS 90 III),trapz(tpDSS 90 IV),tra
pz(tpDSS 90 V),trapz(tpDSS 90 VI),trapz(tpDSS 90 VII),trapz(tpDSS 90 VI
II),trapz(tpDSS 90 IX)];
area loc 90=[trapz(pmax 90 caseII),trapz(pmax 90 caseIII),trapz(pmax 90
caseIV), trapz(pmax 90 caseV), trapz(pmax 90 caseVI), trapz(pmax 90 caseV
II),trapz(pmax 90 caseVIII),trapz(pmax 90 caseIX)];
area 1sun 90=area 1sun 90/1000000;
area loc 90=area loc 90/1000000;
% figure
% plot(d,area 1sun 90)
% hold on
% figure
% subplot(3,1,1)
plot(d,area loc 90,'r')
hold on
% Temperature Effect
% T loc=ANCHORAGE INTL ARPT AL1(1:8760,3); %702730
% T loc=CASA GRANDE MUNI AZ1(1:8760,3);
                                           8722748
T loc=APALACHICOLA MUNI FL1(1:8760,3);
                                           %722200
% T loc=ASPEN PITKIN CO1(1:8760,3);
                                            8724676
if T loc==ANCHORAGE INTL ARPT AL1(1:8760,3);
counter caselocX new=ones(8760,1);
j=32;
for j=32:8640:length(counter caselocX new)
    counter caselocX new(j)=2;
    counter caselocX new(j+1)=0;
end
end
if T loc==CASA GRANDE MUNI AZ1(1:8760,3)
counter caselocX new=ones(8760,1);
j=32;
```

```
for j=32:24:length(counter caselocX new)
    counter caselocX new(j)=2;
    counter caselocX new(j+1)=0;
end
end
if T loc==APALACHICOLA MUNI FL1(1:8760,3)
counter caselocX new=ones(8760,1);
j=32;
for j=32:72:length(counter caselocX new)
    counter caselocX new(j)=2;
    counter caselocX new(j+1)=0;
end
end
if T loc==ASPEN PITKIN CO1(1:8760,3);
counter caselocX new=ones(8760,1);
j=32;
for j=32:72:length(counter caselocX new)
    counter_caselocX_new(j)=2;
    counter_caselocX_new(j+1)=0;
end
end
% T loc1=T loc.';
T loc=T loc+273;
% T loc=T loc+298;
% T loc=T loc+323;
% T loc=T loc+363;
for i=1:length(T loc)
    if T loc(i) <= 323
        kdss loc(i)=kdss25+(kdss inc1/T inc1)*(T loc(i)-T 25);
        udss loc(i)=udss25+(udss inc1/T inc1)*(T loc(i)-T 25);
    else
        kdss_loc(i)=kdss50+(kdss_inc2/T_inc2)*(T_loc(i)-T_50);
        udss loc(i)=udss50+(udss inc2/T inc2)*(T loc(i)-T 50);
    end
    if udss loc(i) <=0
        udss loc(i)=0;
    end
    if kdss loc(i)>=0.4642
        kdss loc(i)=0.4642;
    end
00
      if kdss loc(i)>=0.345
90
          kdss loc(i)=0.345;
00
      end
end
for i=1:length(kdss loc)
tpDSS loc(i)=pref/(1+gamma*(T ref-T loc(i)))-(kdss loc(i)*pref)*(1-
exp((-udss loc(i))*t(i)));
end
pDSS loc=tpDSS loc.';
```

```
% case II: under normal sun without aneealing
pmax loc caseII=(pDSS loc).*((act dat1(1:8760,1)).*(1./(1+delta*(log(1.
/act dat1(1:8760,1)))));
% case-III: annealing once per 2 days
j=1;
for i=1:8760
    if counter caseIII new(i) == 1
    tpDSS loc III(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caseIII new(i)==2
    tpDSS loc III(i)=.83*tpDSS loc III(i-1);
    else
    tpDSS loc III(i)=.946*pref/(1+gamma*(T ref-T loc(i)));
    if T loc(i) <= 313
        j=19;
    elseif (T loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseIII=(tpDSS loc III').*((act dat1(1:8760,1)).*(1./(1+delta*
(log(1./act dat1(1:8760,1)))));
% case-IV: annealing once per day
j=1;
for i=1:8760
    if counter caseIV new(i) == 1
    tpDSS loc IV(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caseIV new(i)==2
    tpDSS loc IV(i)=.83*tpDSS loc IV(i-1);
    else
    tpDSS_loc_IV(i) = .946*pref/(1+gamma*(T_ref-T_loc(i)));
    if T loc(i) <= 313
        j=19;
    elseif (T_loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        i=6;
    end
```

```
end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS_25_III(1,1:192),[0 5.278]))
% hold on
pmax_loc_caseIV=(tpDSS_loc_IV').*((act_dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
% case-V: annealing twice per day
j=1;
for i=1:8760
    if counter_caseV_new(i) ==1
    tpDSS loc V(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caseV new(i) == 2
    tpDSS loc V(i)=.83*tpDSS loc V(i-1);
    else
    tpDSS loc V(i)=.946*pref/(1+gamma*(T ref-T loc(i)));
    if T loc(i) <= 313
        _____;
    elseif (T loc(i)>313) && (T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseV=(tpDSS loc V').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
% case-VI: annealing thrice per day
j=1;
for i=1:8760
    if counter caseVI new(i) ==1
    tpDSS loc VI(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caseVI new(i) == 2
    tpDSS loc VI(i)=.83*tpDSS loc VI(i-1);
    else
```

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```

```
tpDSS loc VI(i)=.946*pref/(1+gamma*(T ref-T loc(i)));
    if T loc(i) <= 313
        j=19;
    elseif (T loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseVI=(tpDSS loc VI').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
% case-VII: annealing four times per day
j=1;
for i=1:8760
    if counter caseVII new(i) == 1
    tpDSS loc VII(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caseVII new(i) == 2
    tpDSS loc VII(i)=.83*tpDSS loc VII(i-1);
    else
    tpDSS loc VII(i)=.946*pref/(1+gamma*(T ref-T loc(i)));
    if T loc(i) <= 313
        j=19;
    elseif (T loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax_loc_caseVII=(tpDSS_loc_VII').*((act_dat1(1:8760,1)).*(1./(1+delta*
(log(1./act dat1(1:8760,1)))));
% case-VIII: annealing five times per day
```

```
j=1;
```

```
for i=1:8760
    if counter caseVIII new(i) == 1
    tpDSS loc VIII(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j = j + 1;
    elseif counter caseVIII new(i) == 2
    tpDSS loc VIII(i)=.83*tpDSS loc VIII(i-1);
    else
    tpDSS loc VIII(i)=.946*pref/(1+gamma*(T ref-T loc(i)));
    if T_loc(i) <=313
        j=19;
    elseif (T loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseVIII=(tpDSS loc VIII').*((act dat1(1:8760,1)).*(1./(1+delt
a*(log(1./act dat1(1:8760,1)))));
% case-IX: annealing six times per day
i=1;
for i=1:8760
    if counter caseIX new(i) == 1
    tpDSS loc IX(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss_loc(i))*t(j)));
    j=j+1;
    elseif counter caseIX new(i) == 2
    tpDSS loc IX(i)=.83*tpDSS loc IX(i-1);
    else
    tpDSS_loc_IX(i) = .946*pref/(1+gamma*(T_ref-T_loc(i)));
    if T loc(i) <= 313
        j=19;
    elseif (T loc(i)>313) && (T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
```

```
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseIX=(tpDSS loc IX').*((act dat1(1:8760,1)).*(1./(1+delta*(1
og(1./act dat1(1:8760,1)))));
% case-X: optimized annealing
j=1;
for i=1:8760
    if counter caselocX new(i) ==1
    tpDSS loc X(i)=pref/(1+gamma*(T ref-T loc(i)))-
(kdss loc(i)*pref)*(1-exp((-udss loc(i))*t(j)));
    j=j+1;
    elseif counter caselocX new(i) == 2
    tpDSS loc X(i)=.83*tpDSS loc X(i-1);
    else
    tpDSS loc X(i) = .946*pref/(1+gamma*(T ref-T loc(i)));
    if T_loc(i) <= 313
        j=19;
    elseif (T loc(i)>313)&&(T loc(i)<=343)
        j=11;
    else
        j=6;
    end
    end
end
% figure
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(pDSS 25(1:192,1),[0 5.278]),'g')
% hold on
% subplot(3,1,1)
% plot(t(1,1:192),mat2gray(tpDSS 25 III(1,1:192),[0 5.278]))
% hold on
pmax loc caseX=(tpDSS loc X').*((act dat1(1:8760,1)).*(1./(1+delta*(log
(1./act dat1(1:8760,1)))));
% analysis
d=[0,0.5,1,2,3,4,5,6 7]; % no of annealing per day
area 1sun ranloc=[trapz(pDSS loc),trapz(tpDSS loc III),trapz(tpDSS loc
IV),trapz(tpDSS loc V),trapz(tpDSS loc VI),trapz(tpDSS loc VII),trapz(t
pDSS loc VIII),trapz(tpDSS loc IX)];
area ranloc=[trapz(pmax loc caseII),trapz(pmax loc caseIII),trapz(pmax
loc caseIV),trapz(pmax loc caseV),trapz(pmax loc caseVI),trapz(pmax loc
caseVII), trapz (pmax loc caseVIII), trapz (pmax loc caseIX), trapz (pmax lo
c caseX)];
area 1sun ranloc=area 1sun ranloc/1000000;
area ranloc=area ranloc/1000000;
% figure
% plot(d, area 1sun 25)
% hold on
figure
% subplot(3,1,1)
```

plot(d,area_ranloc,'k')
hold on